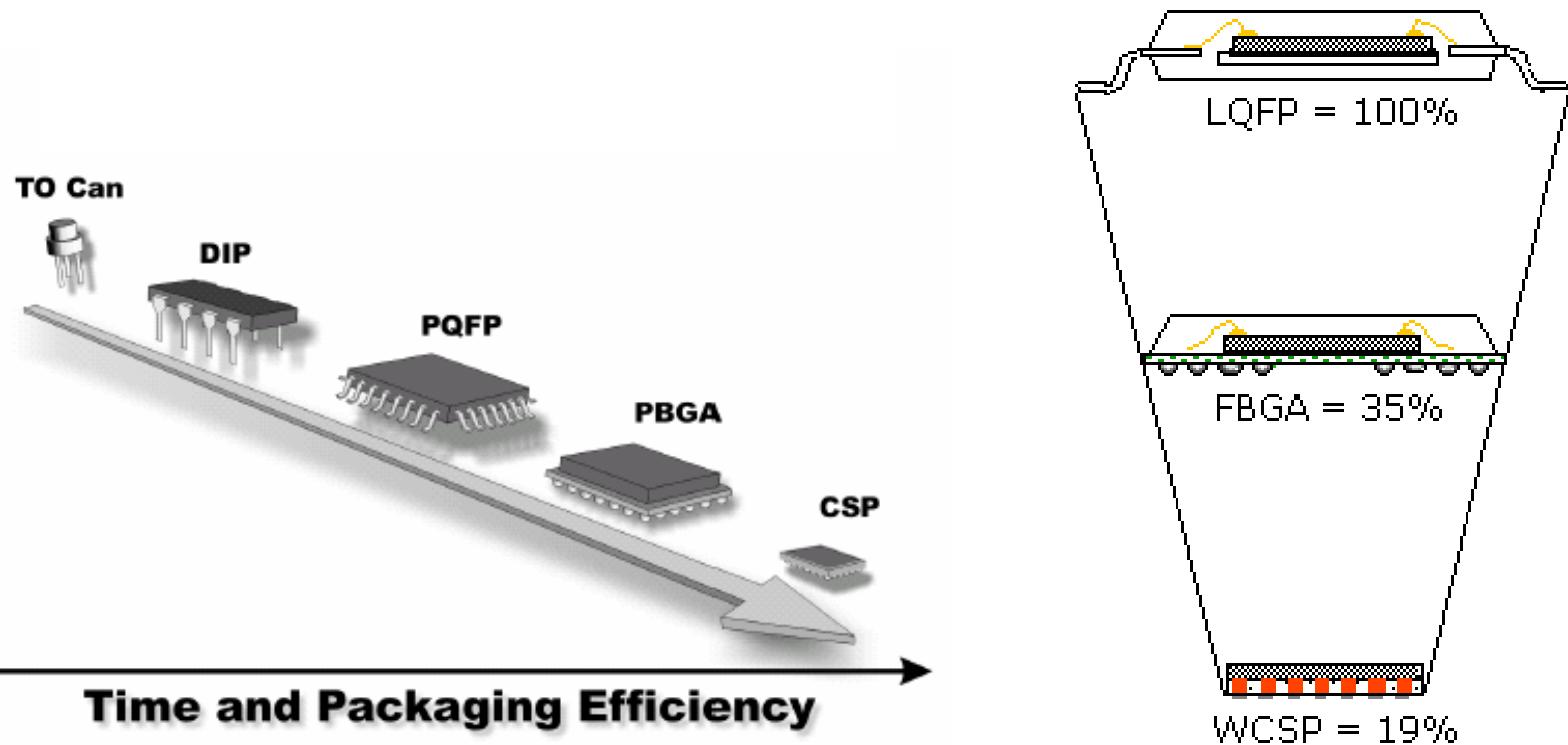


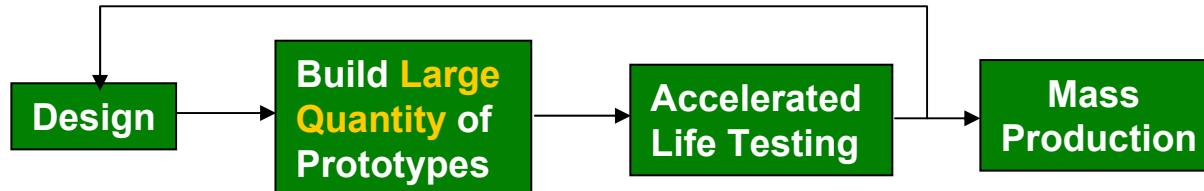
◆ *Introduction*

◆ IC Packaging Evolution



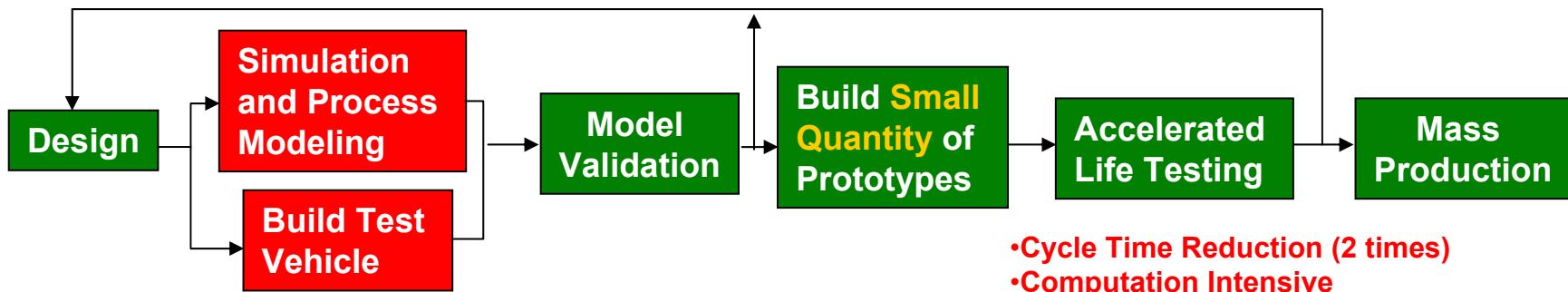
Reliability Modeling vs. Reliability Testing

1. Reliability Testing (Conventional Procedure, DOE)



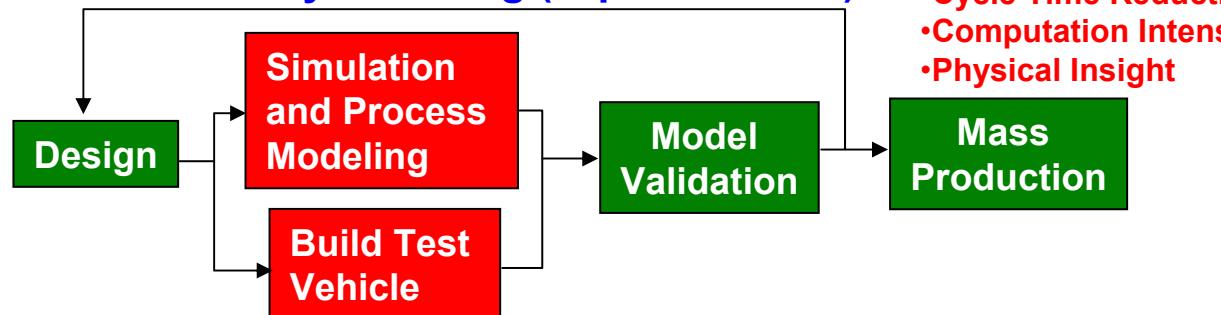
- Labor Intensive
- Long Cycle Time (e.g. a typical cellular phone requires 4-7 iterations, 4-8 weeks per iteration)
- Lack of Physical Insight

2. Reliability Modeling (Optimized Design Procedure)



- Cycle Time Reduction (2 times)
- Computation Intensive

3. Reliability Modeling (Optimal Goal)



- Cycle Time Reduction (10 times)
- Computation Intensive
- Physical Insight

Software Tools for MEMS

☞ Layout tools

- ⇒ MEMCAD
- ⇒ Intellisuite
- ⇒ L-Edit

☞ Process Simulation Tools

- ⇒ Avant! TCAD(TSUPREM-4 for semiconductor)
- ⇒ Intellisuite

☞ Device Simulation Tools

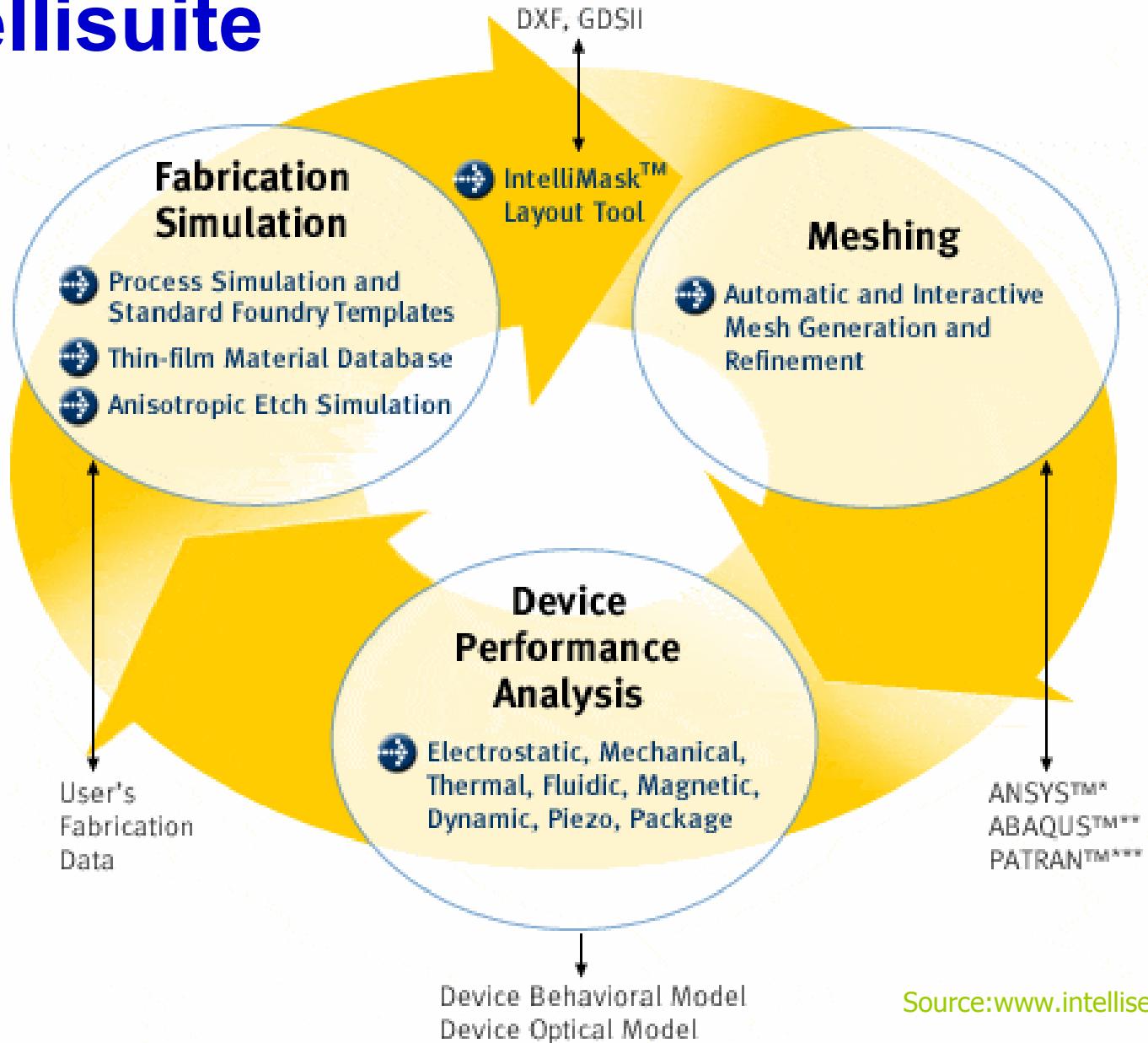
- ⇒ MEMCAD
- ⇒ Intellisuite
- ⇒ ANSYS
- ⇒ NASTRAN
- ⇒ ABAQUS



MEMS



Intellisuite

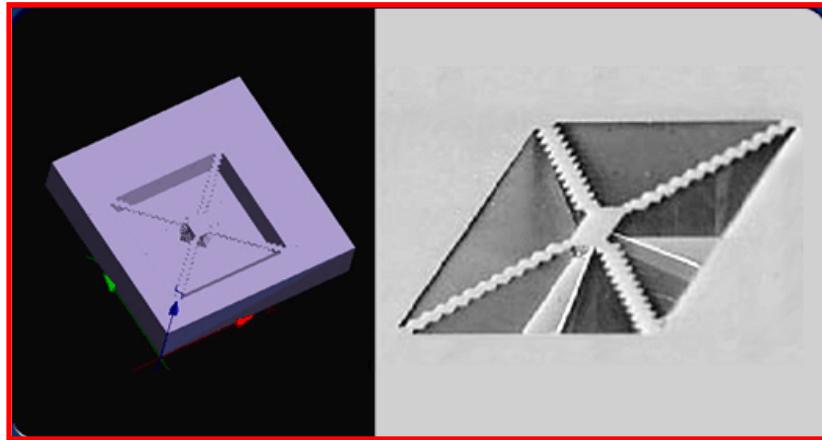


Intellisuite

--Fabrication simulation

Process database & table

The screenshot shows the IntelliFab software interface with a menu bar (File, Process, Construct, Simulation, Database, Help) and a toolbar. The left pane displays a hierarchical process database with categories like Deposition, Etch, and Resist. The right pane lists specific process definitions, such as 'Definition Si Czochralski 100', 'Etch Si Clean Pirahna', and 'Deposition Si3N4 PECVD Ar'. A red box highlights the central list area.



Thin-film Material Properties

The screenshot shows the MEMaterial software interface with a menu bar (File, Edit, View, Show, Data, Window, Help) and a toolbar. The central area displays material properties for 'Si3N4 PECVD Ar' with the following data:

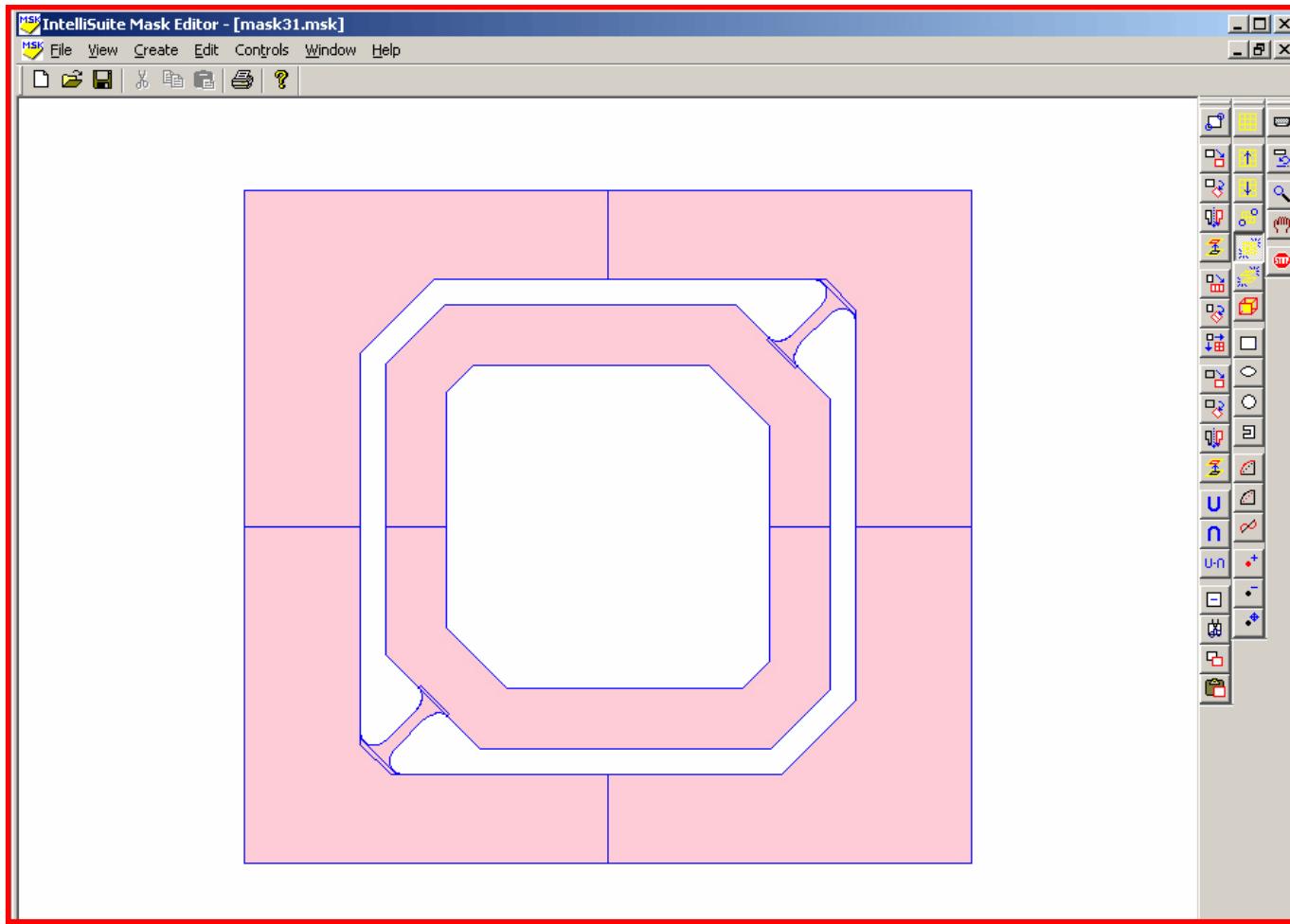
Property	Value	Units	Comments
STRESS	500.	MPa	meas
DENSITY	2.55	g/cm ³	meas
CTE _{Exp}	16.	10 ⁽⁻⁷⁾ /C	meas
YOUNG	300.	GPa	meas
POISSON	0.27	const	meas
REFR_IN	2.05	const	meas

Anisotropic Etch Simulation(AnisE)



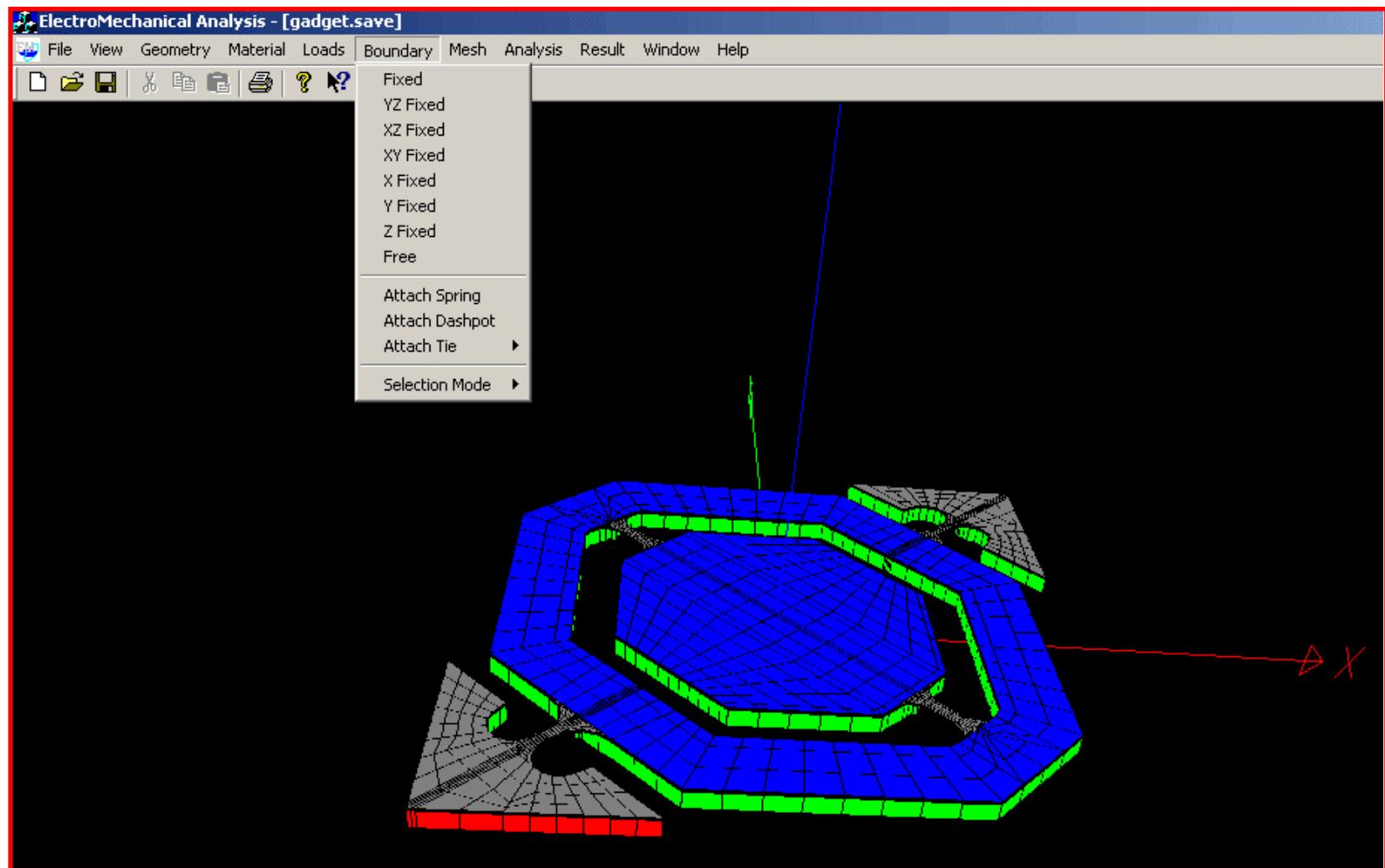
Intellisuite

--Mask Layout



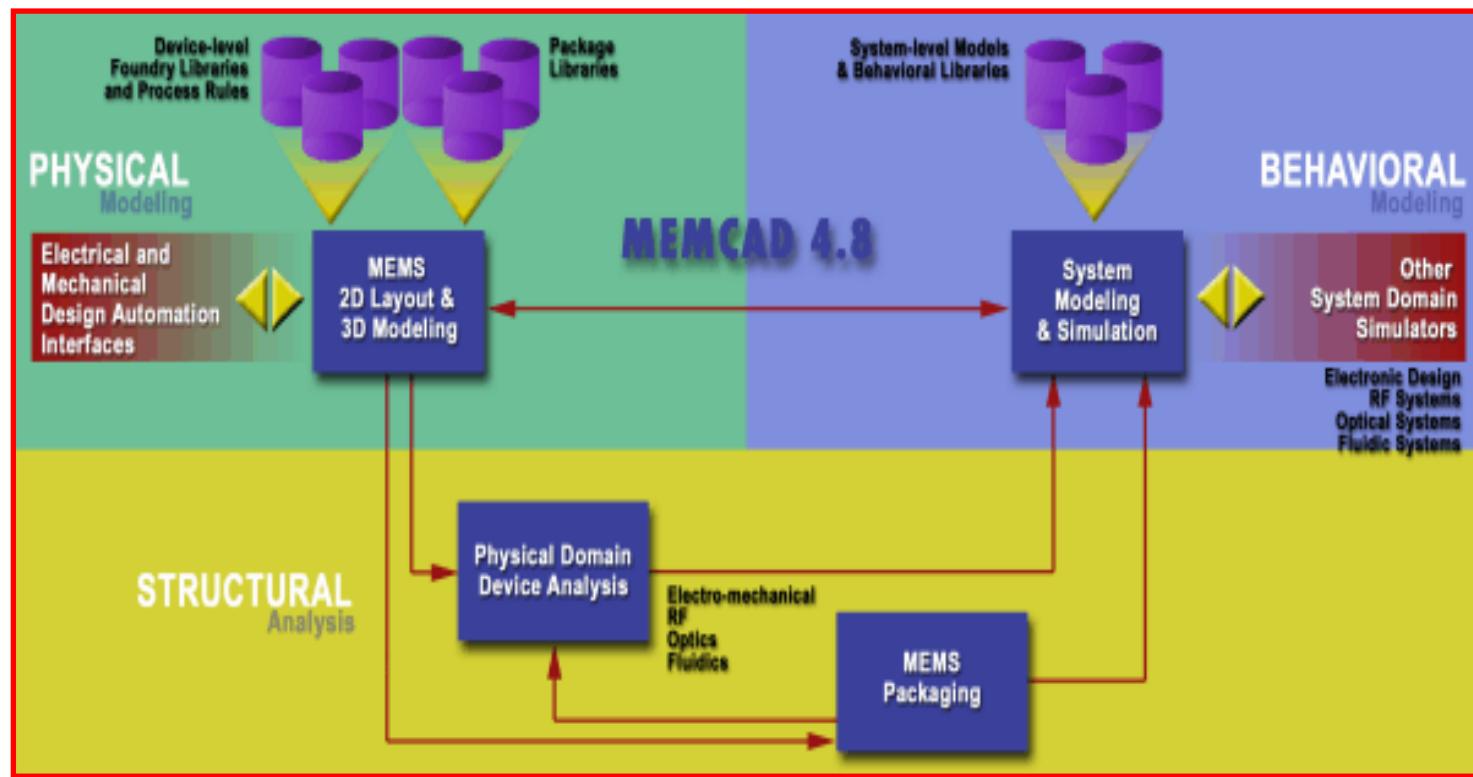
Intellisuite

--Performance Analysis



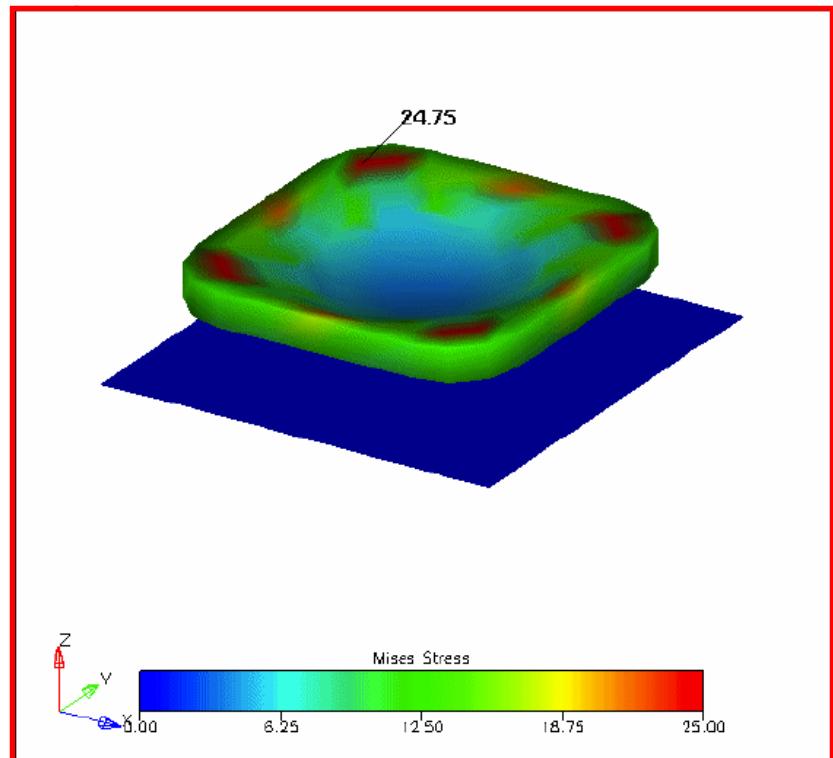
MEMCAD

- Device layout and construction
- Device modeling and simulation
- System modeling and simulation

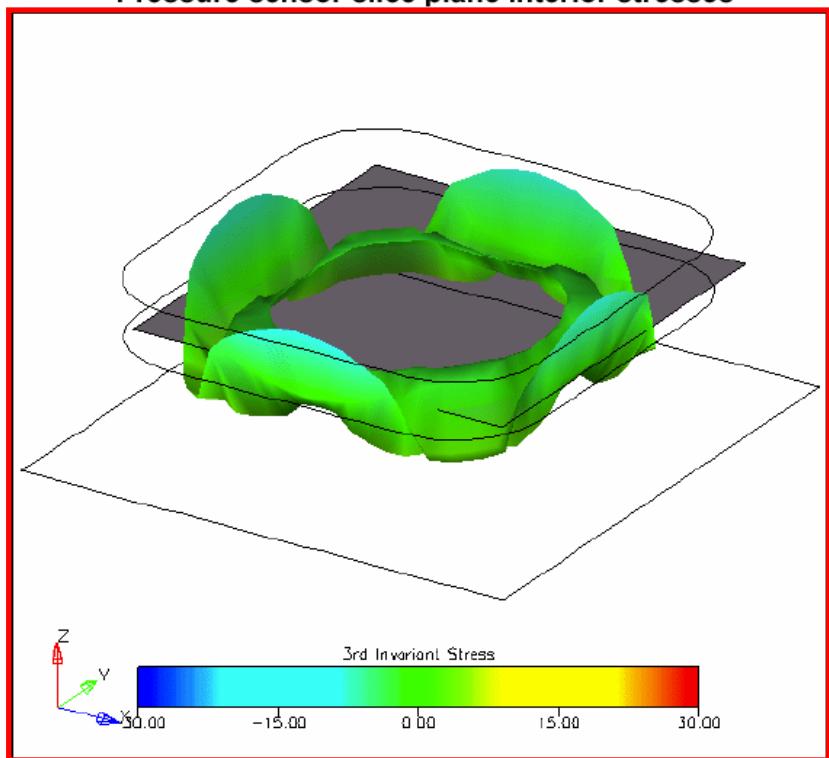


MEMCAD

Visualizer view of a MemMech solution



Pressure sensor slice plane interior stresses



Process Simulation Tool



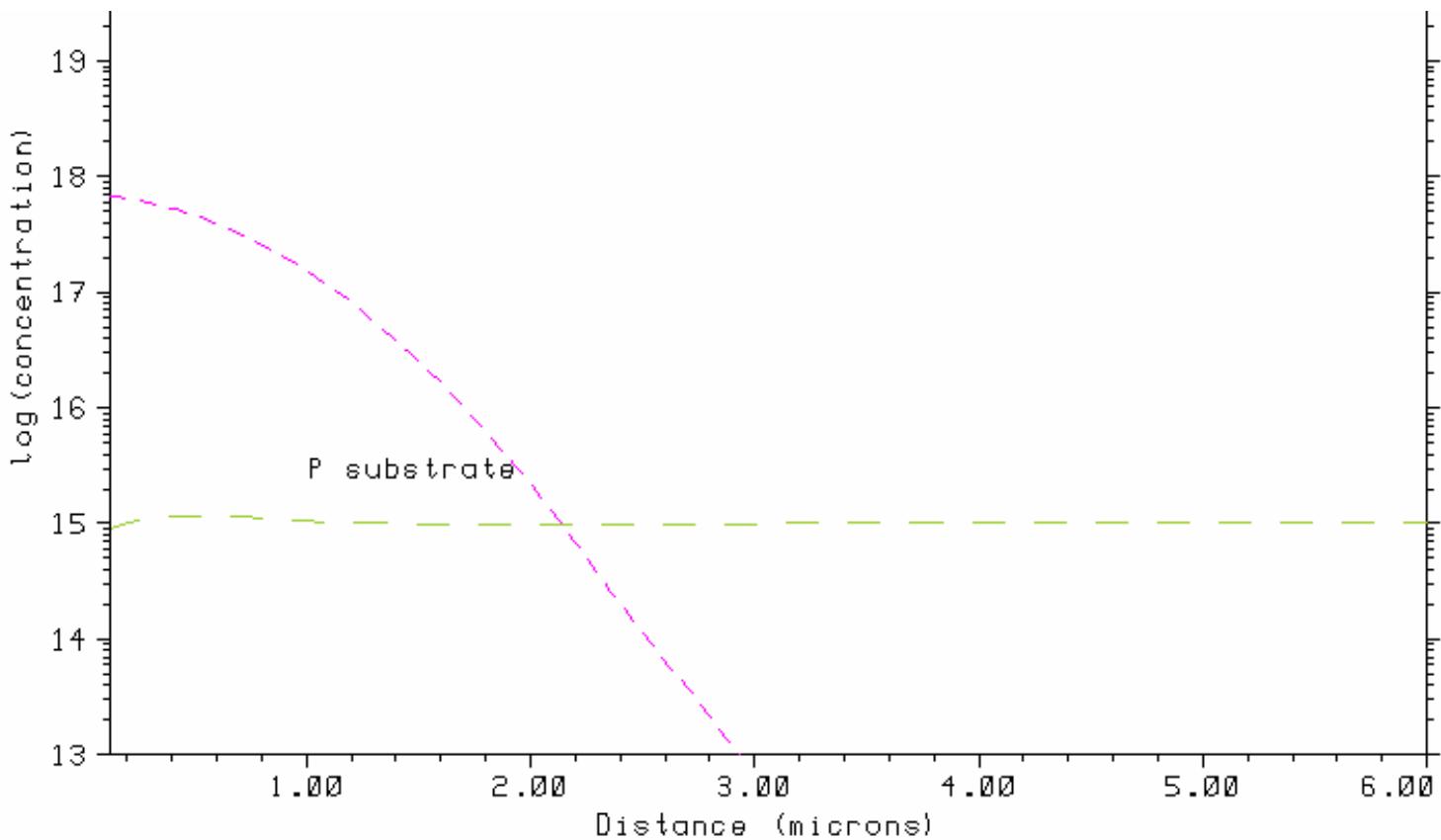
TSUPREM-4

- One and two-dimensional process simulation program
- Simulation etching, deposition, lithography, implantation, diffusion, epitaxy
- Output
 - ⇒ Boundary of the various layers of material in the structure
 - ⇒ Distribution of impurities within each layer
 - ⇒ Stresses produced by oxidation, thermal cycling, or film deposition



TSUPREM-4

--One Dimension Simulation



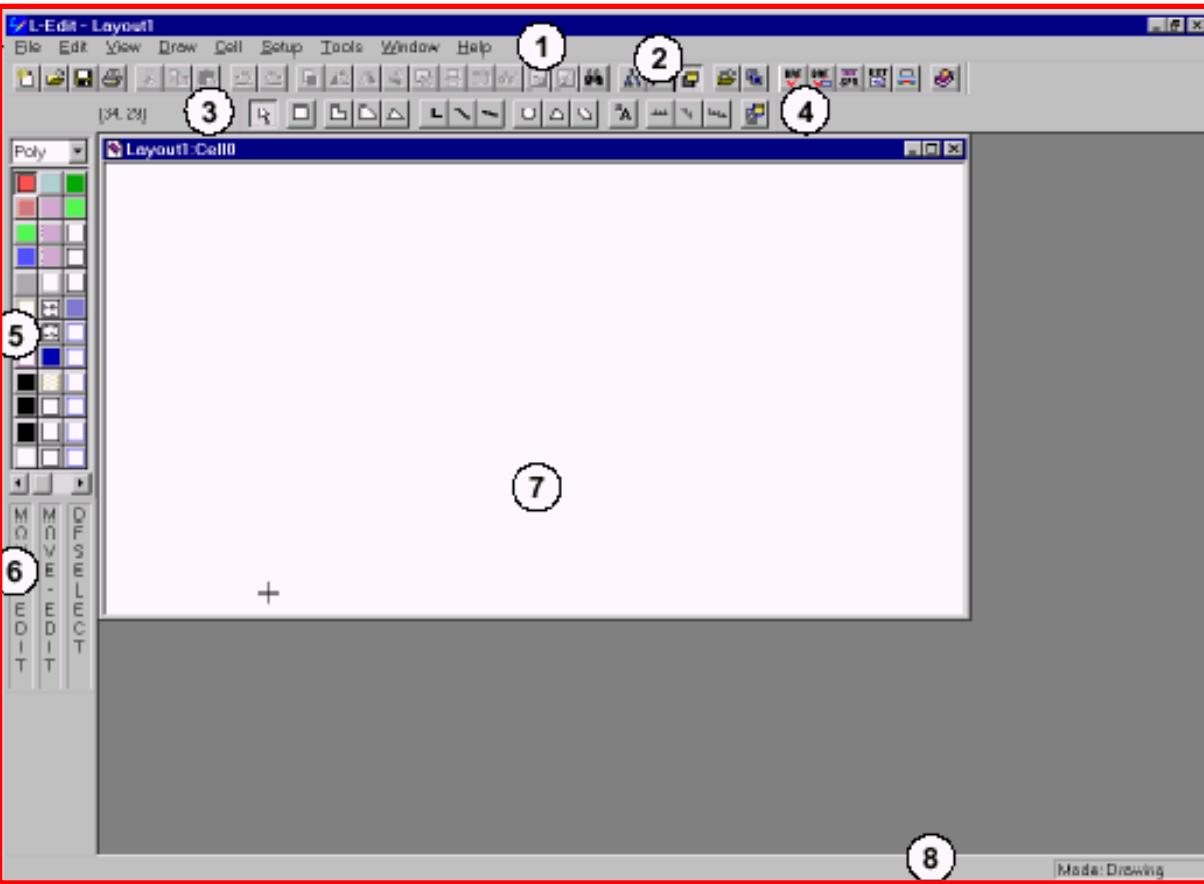
Layout Tool



L-Edit

--Layout Tool

L-Edit is a computer-aided design tool used to create photolithography masks for integrated circuits and MEMS devices.



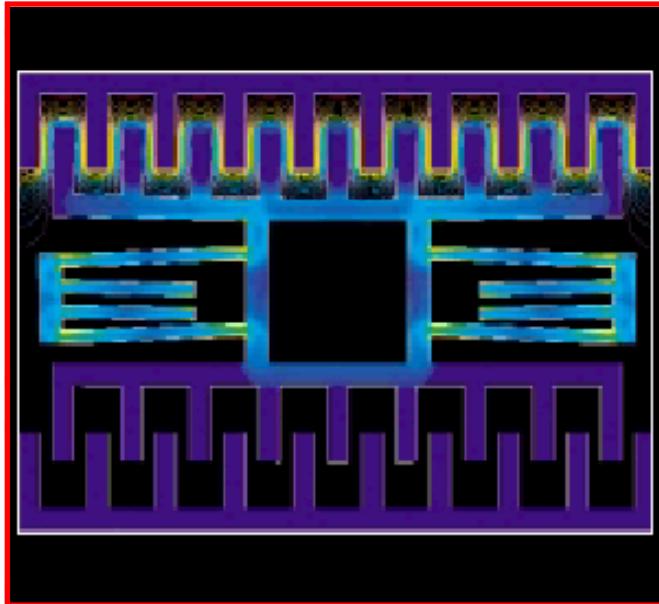
- ① The Menu bar (adjoined to the Title bar).
- ② The Standard toolbar.
- ③ The Locator.
- ④ The Drawing toolbar.
- ⑤ The Layer Palette.
- ⑥ The Mouse Buttons bar.
- ⑦ The Layout Window.
- ⑧ The Status bar.

Finite Element Program

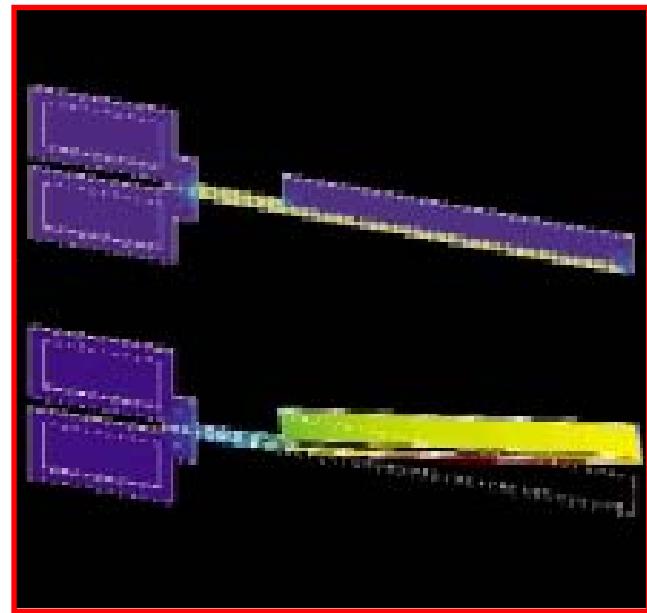


ANSYS

- Structure analysis
- Thermal analysis
- Electromagnetics analysis
- CFD analysis
- Acoustic analysis



MEMS comb drive has been modeled using electrostatic-structural coupling.



MEMS thermal-mechanical actuator device

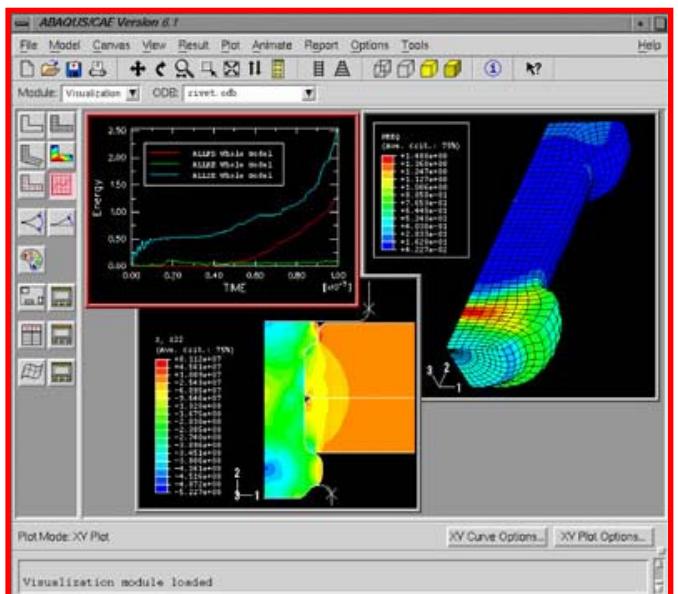
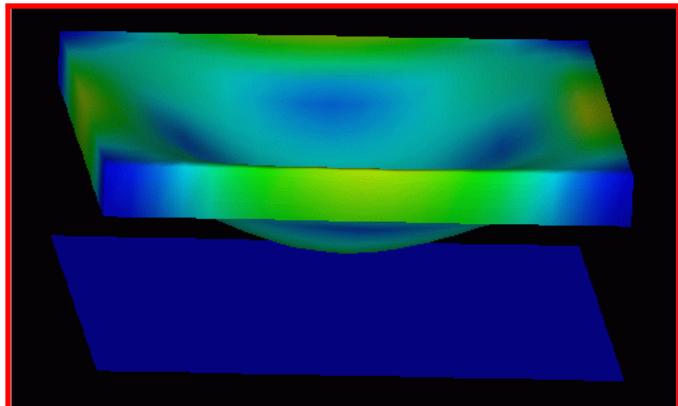
ABAQUS

General Analyses

- Static stress/displacement analysis
- Viscoelastic/viscoplastic response
- Transient dynamic stress/displacement analysis
- Transient or steady-state heat transfer analysis

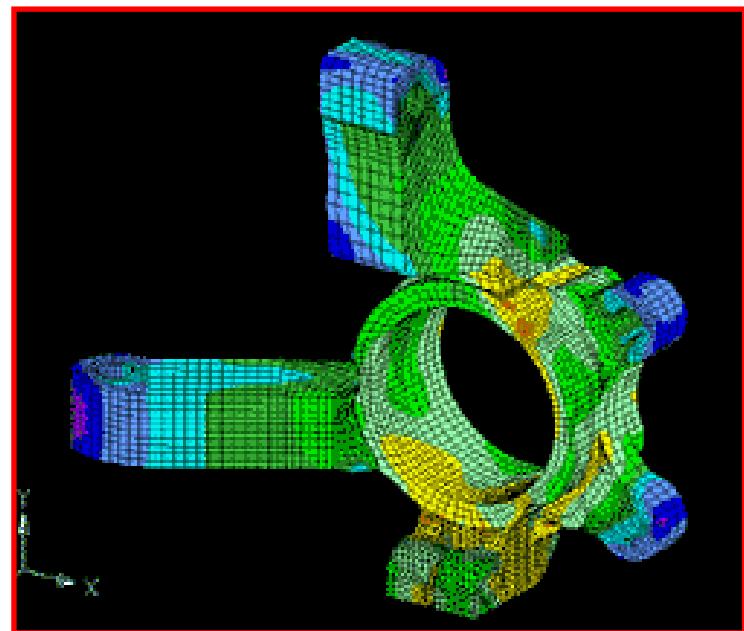
Coupled problems:

- Thermo-mechanical (sequentially or fully coupled)
- Thermo-electrical
- Pore fluid flow-mechanical
- Stress-mass diffusion (sequentially coupled)
- Piezoelectric (linear only)
- Acoustic-mechanical (linear only)



MSN/ANSTRAN

- Linear Static Analysis
- Non-linear Analysis
- Buckling Analysis
- Heat-Transfer Analysis
- Dynamic Analysis
- Optimization Analysis



Other Software Tools for MEMS

- **Anisotropic Etch Simulation**

- ⇒ Anisotropic Crystalline Etch Simulation(ACES)
- ⇒ Anisotropic Silicon Etching Program(ASEP)
- ⇒ SEGS

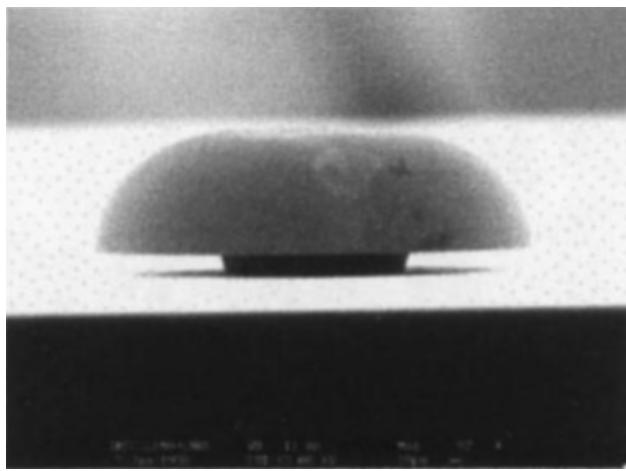
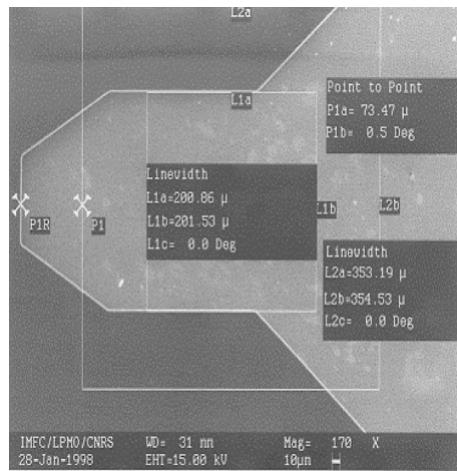
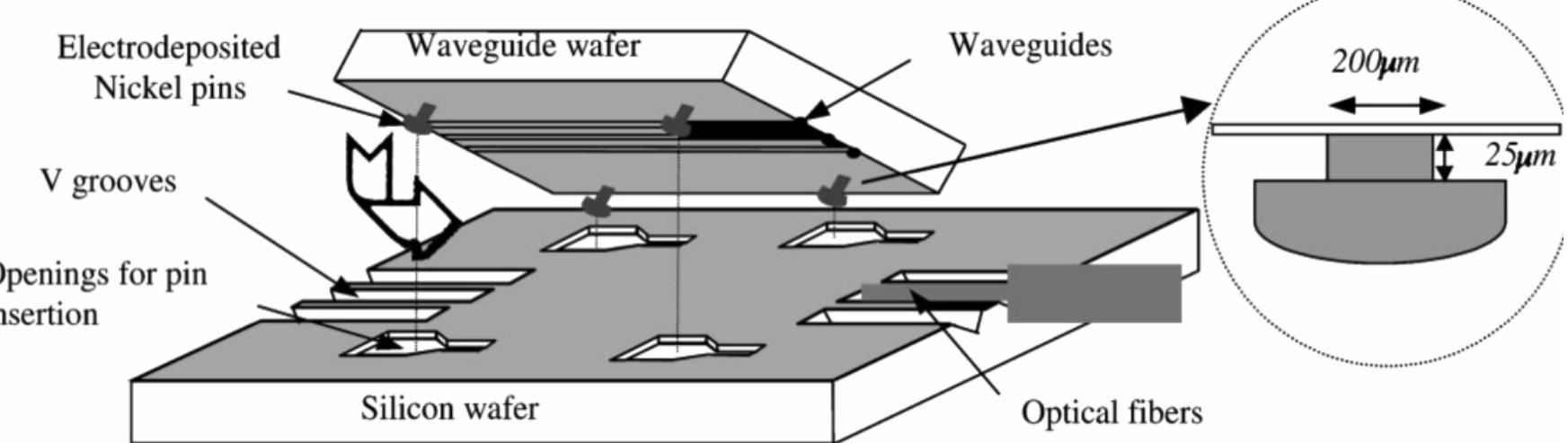
- **Process Simulation**

- ⇒ MEMS Pro
- ⇒ MEMS Xplorer

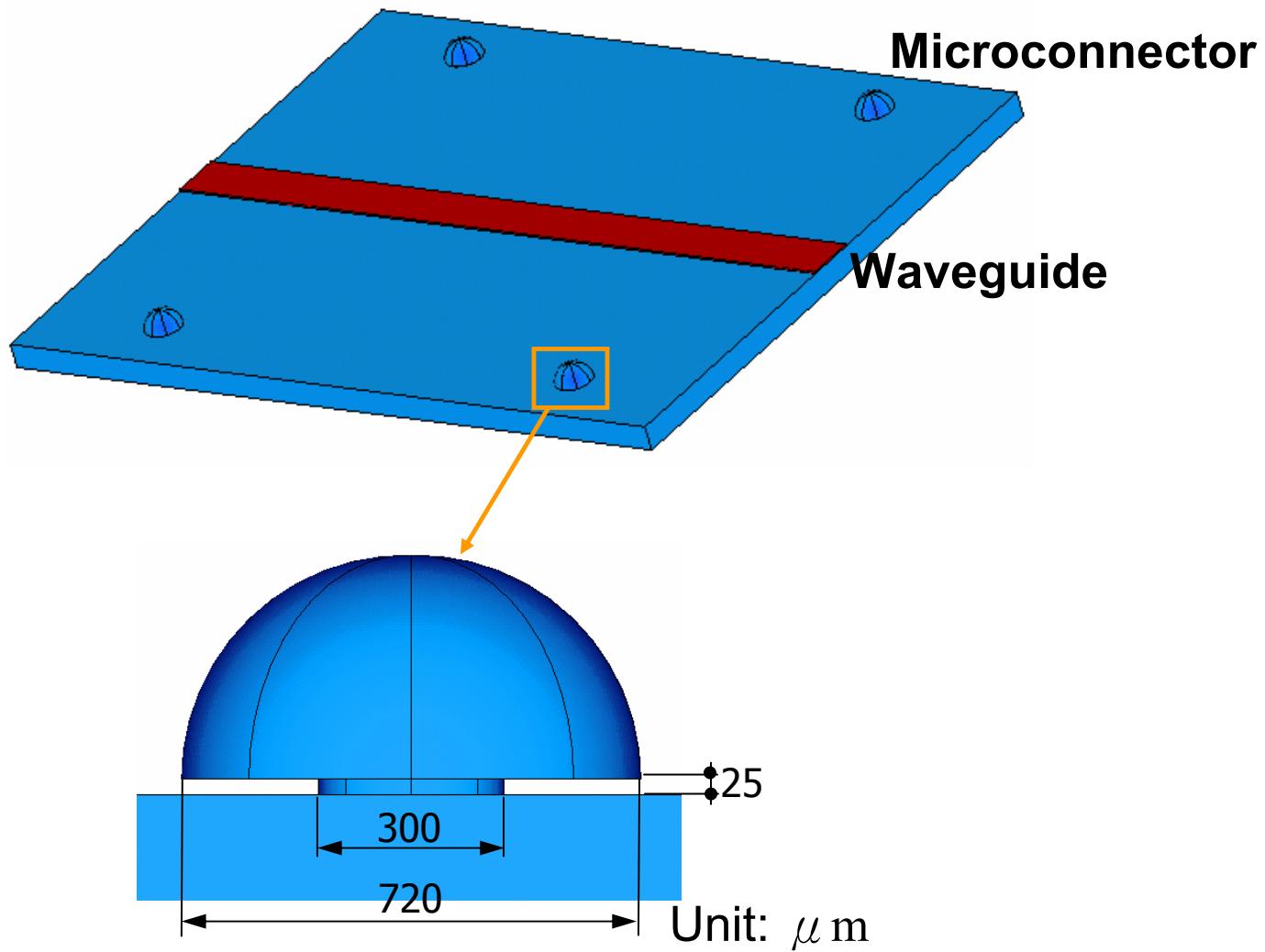
- **Fluid flow Simulation**

- ⇒ CFD-ACE
- ⇒ Flume CAD

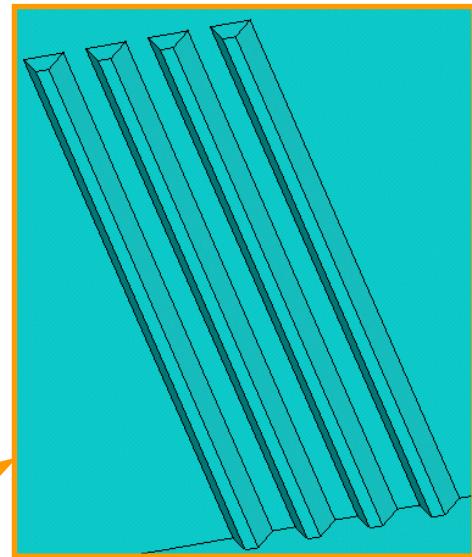
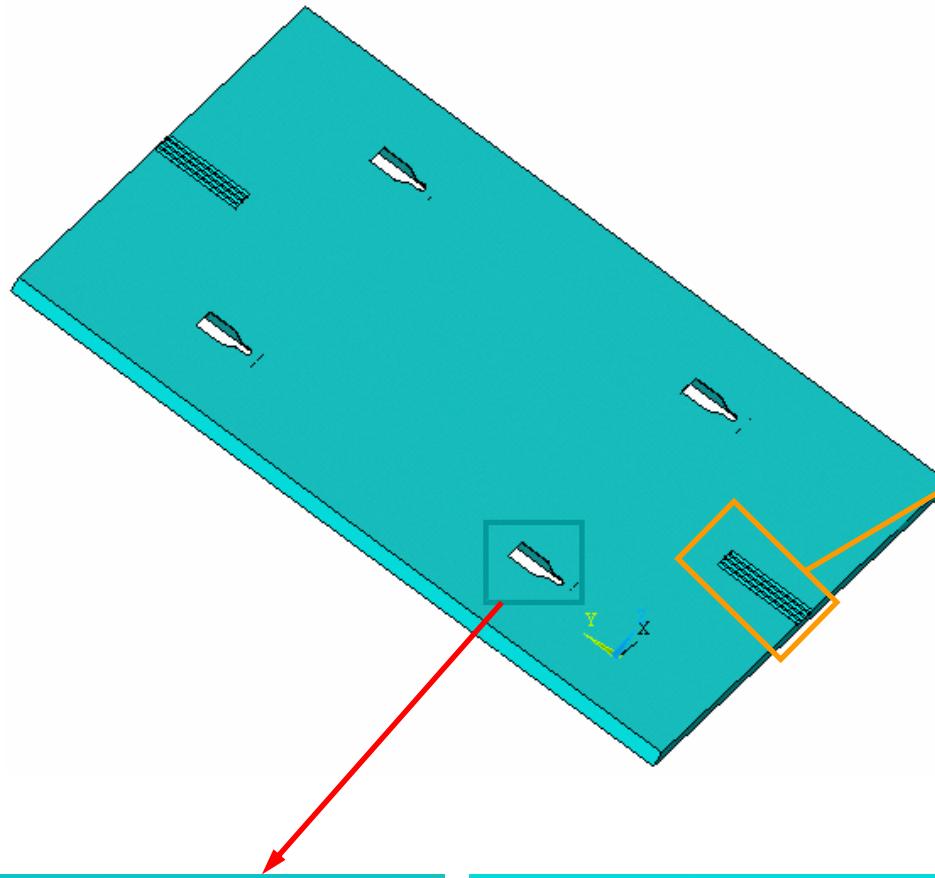
Kaou et al., 2001



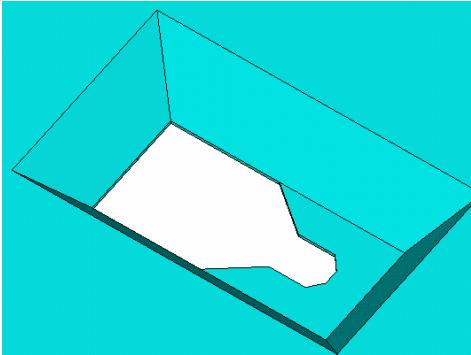
Waveguide Wafer



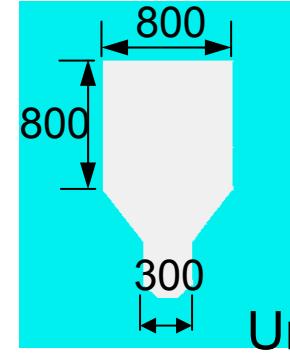
Silicon Wafer



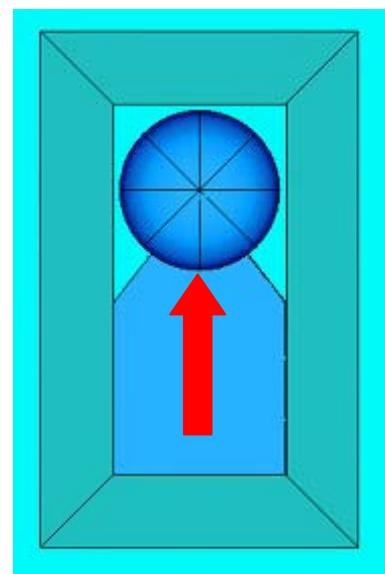
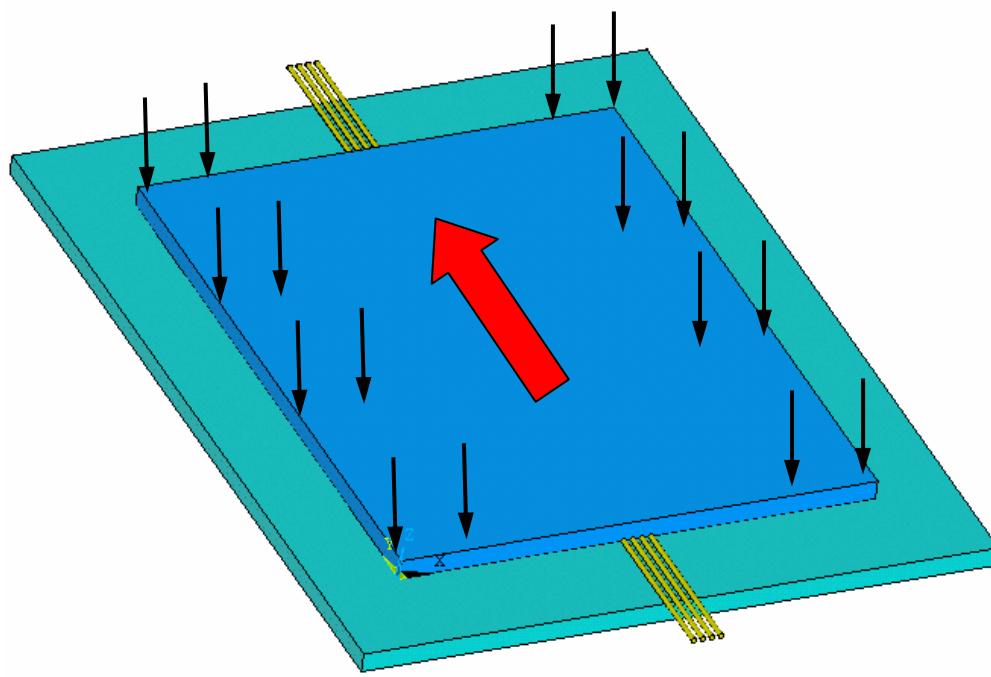
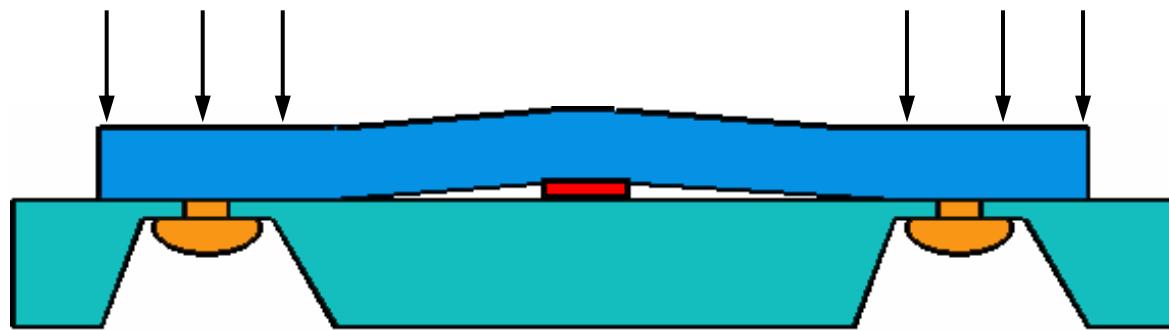
V-Groove



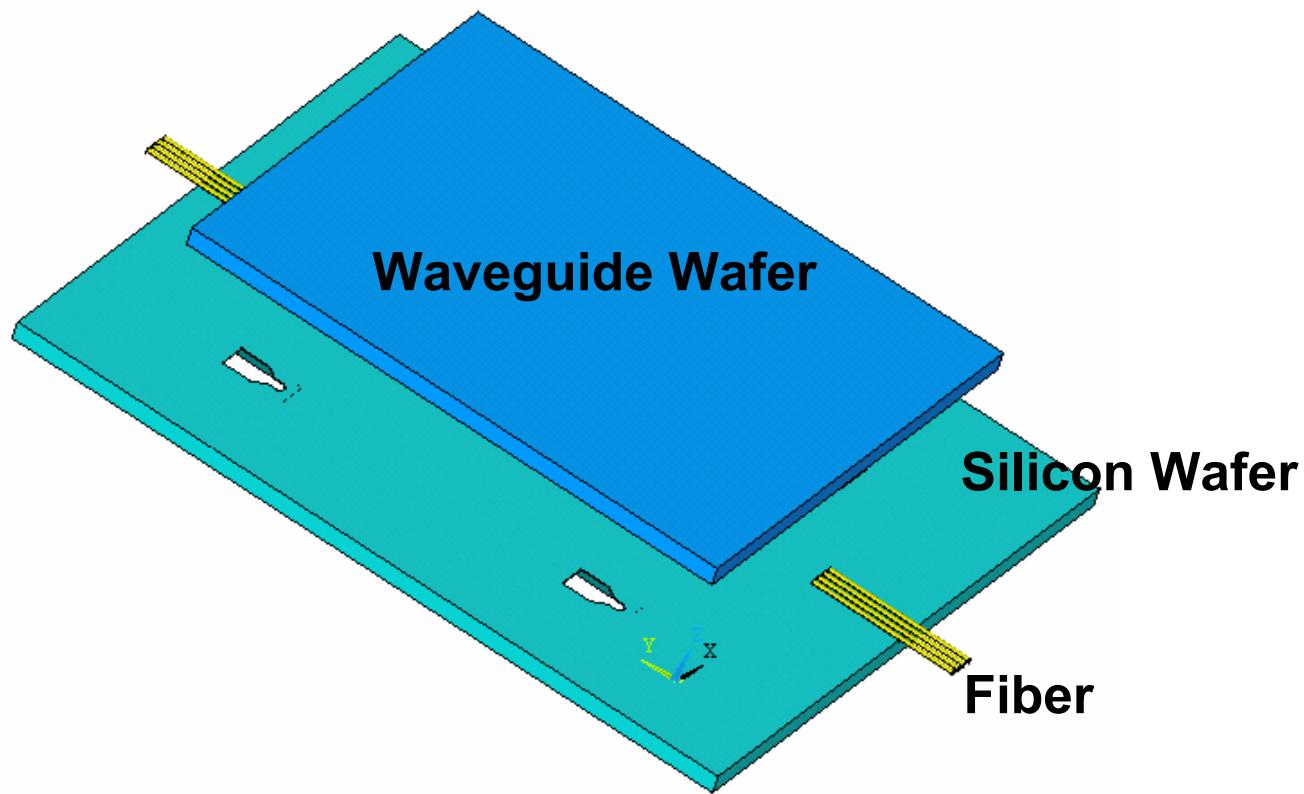
Membrane



Assembly

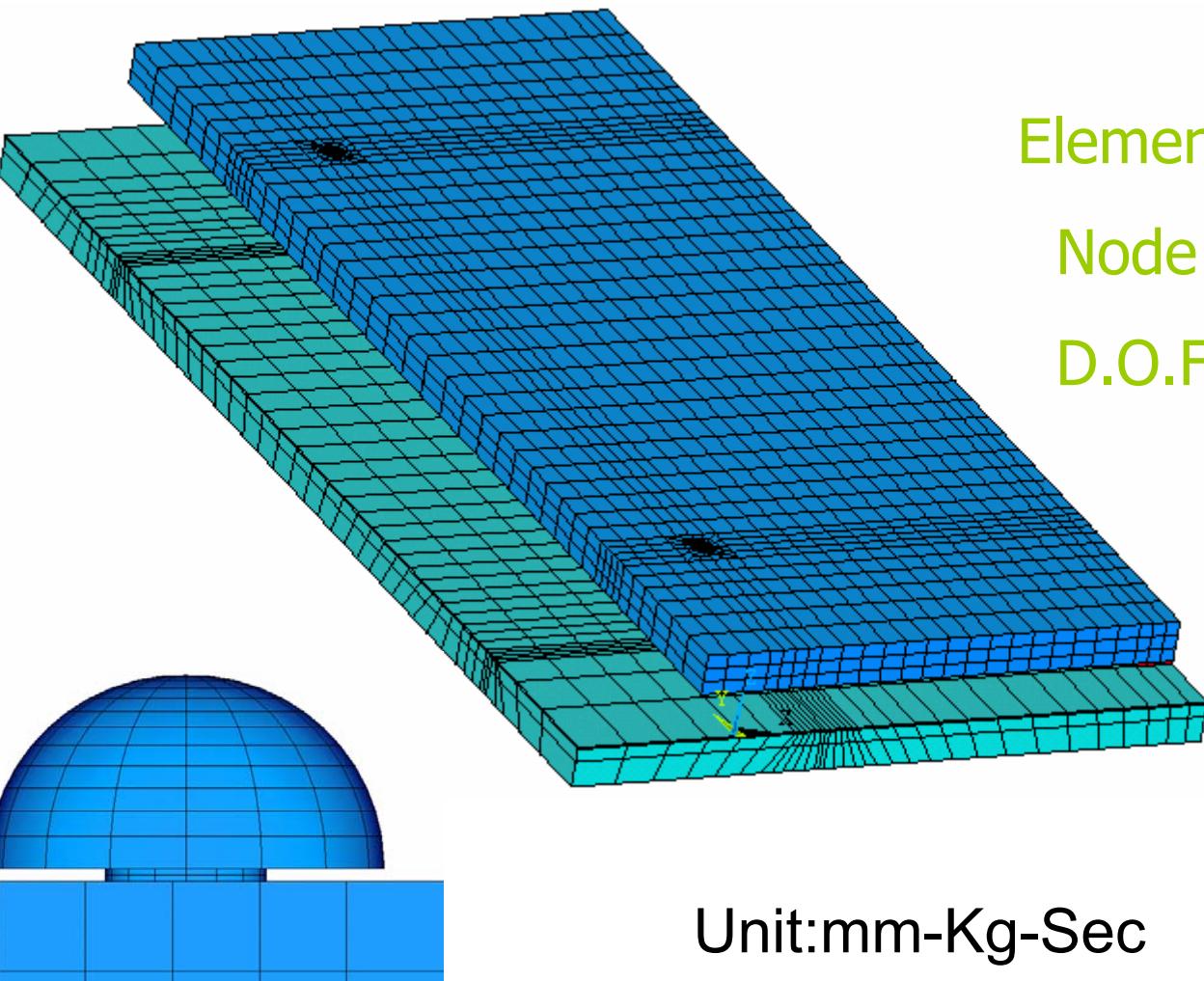


Geometry of Optical Modulus



Finite Element Model

3D Solid Element with one integrated point



Element No : 10,294

Node No : 13,762

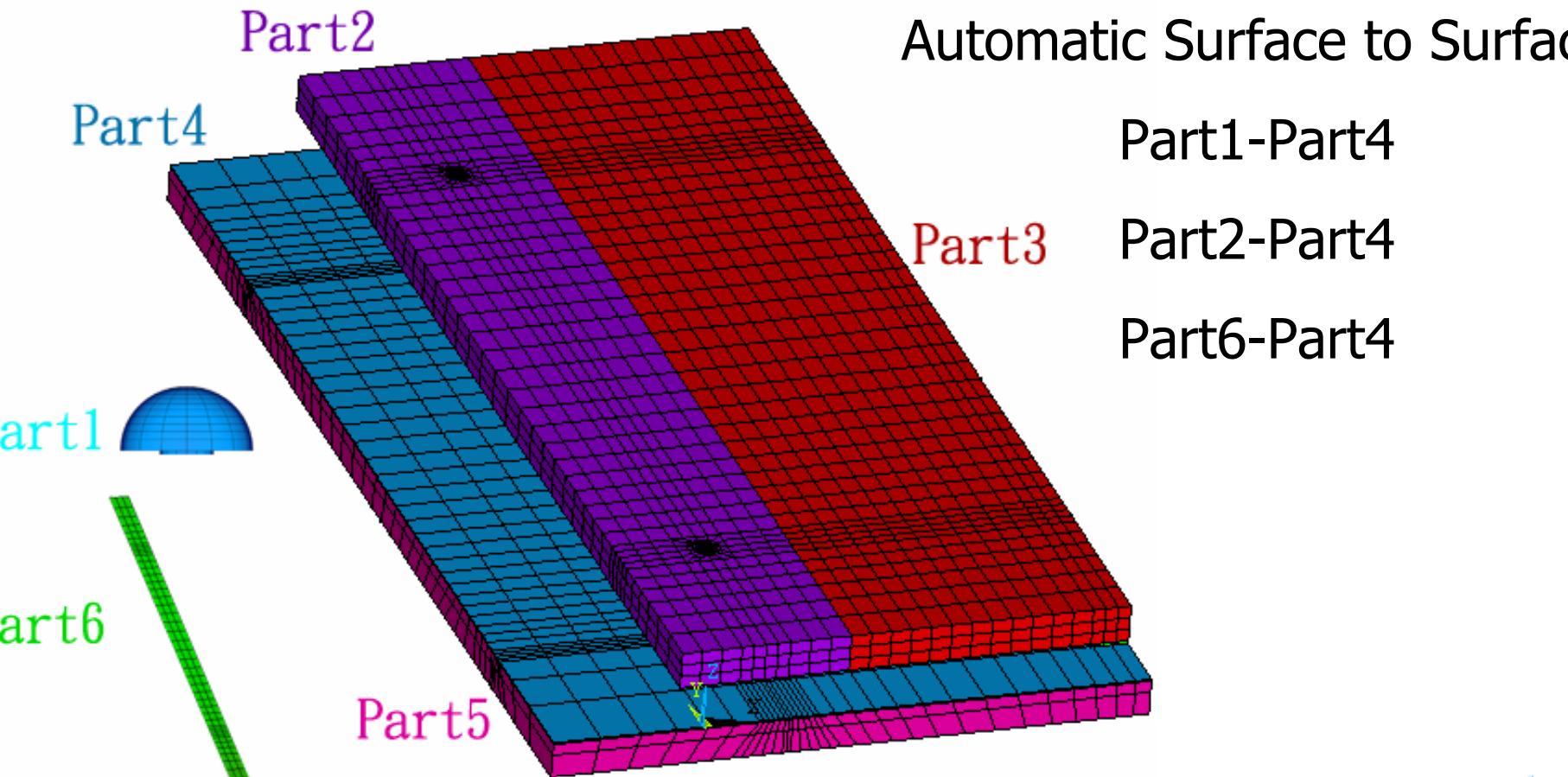
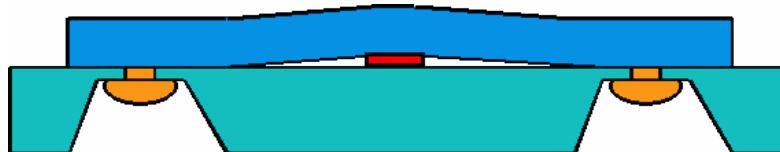
D.O.F. : 41,286

Unit:mm-Kg-Sec

Parameter

Material	Nickel	Silicon
Young's Modulus(GPa)	176.0	112.4
Density(Kg/m ³)	8900	2330
Coefficient of Thermal Expansion(CTE)(ppm)	14	2.62
Possion's Ratio	0.31	0.28

Contact Setting



Automatic Surface to Surface

Part4

Part2

Part1-Part4

Part3

Part2-Part4

Part6-Part4

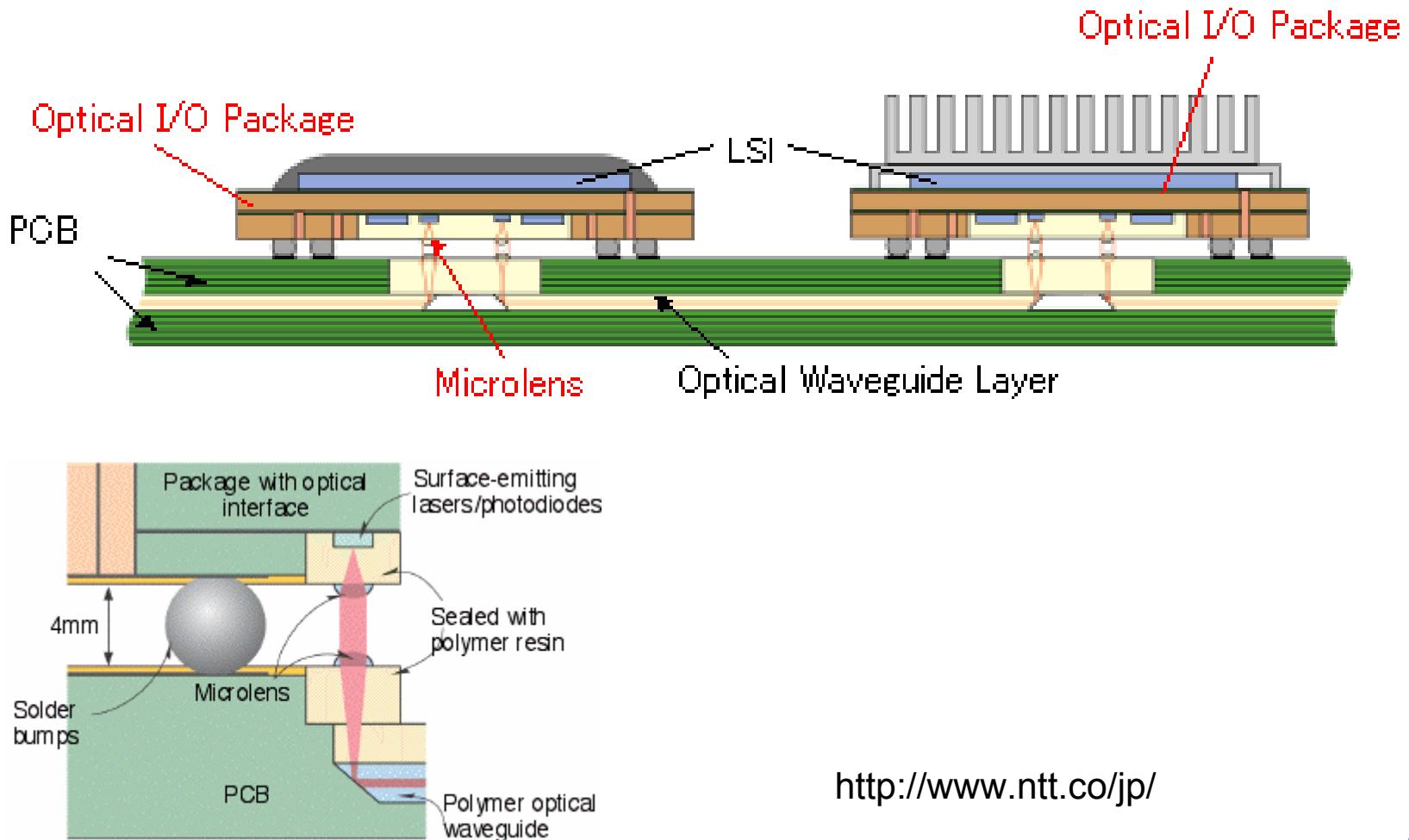
part1

part6

Part5

Introduction

NTT



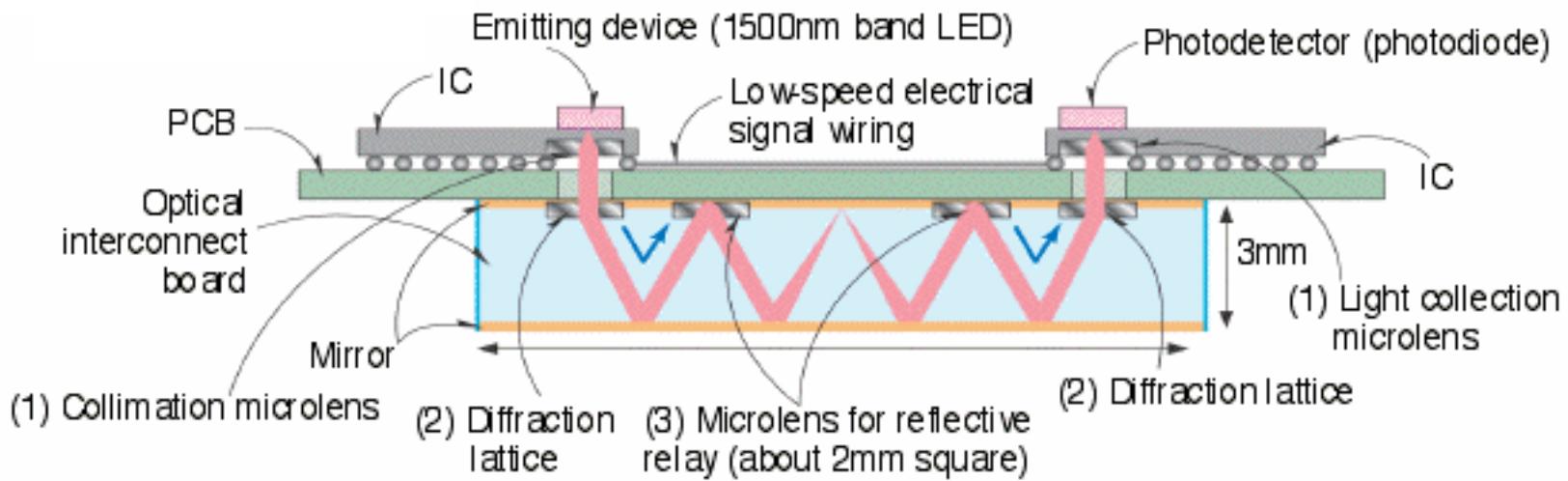
<http://www.ntt.co.jp/>

CSM

OPTIONAL TECHNOLOGY

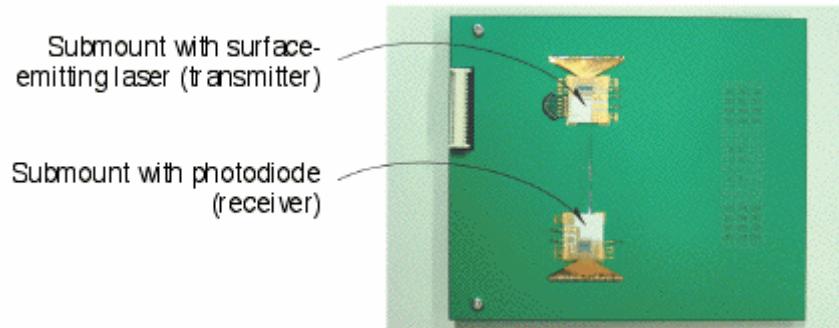
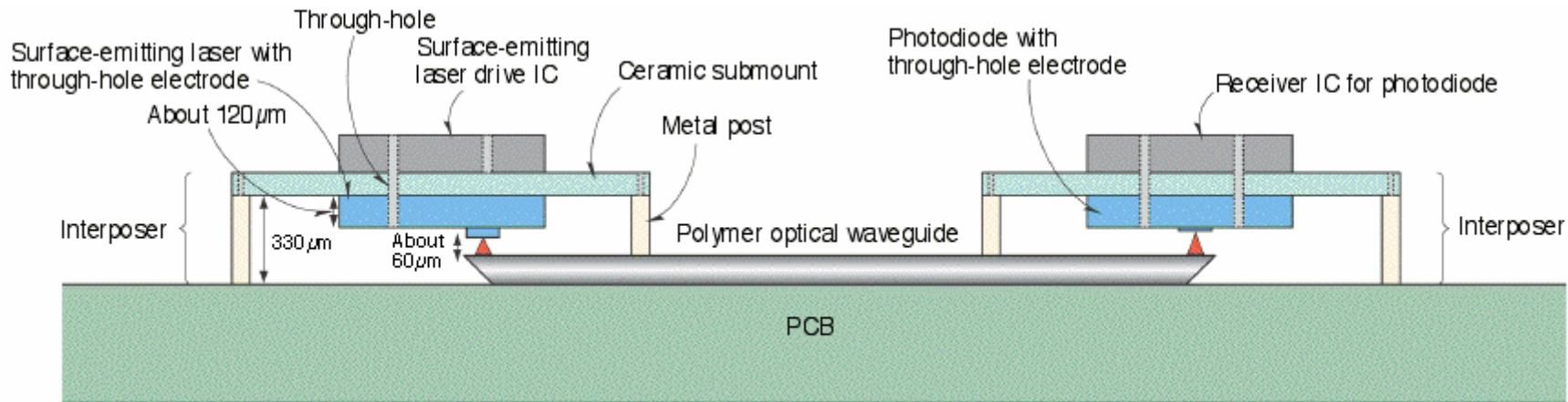
Introduction

Oki



Introduction

ASET

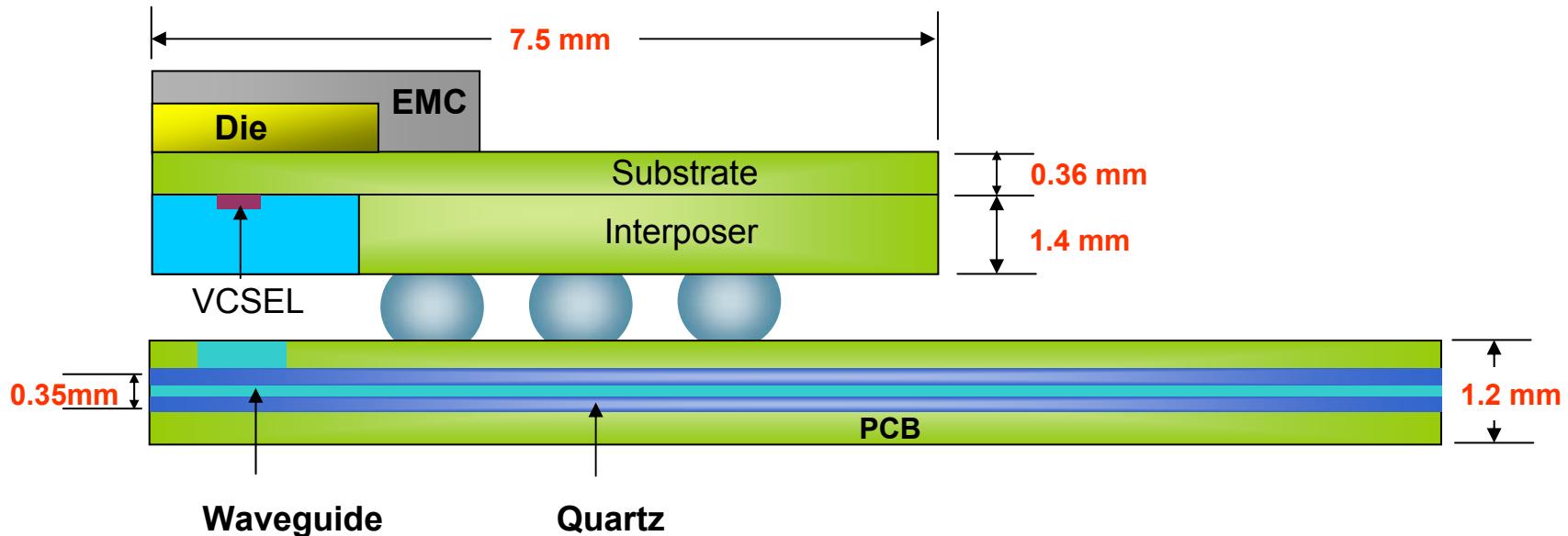


<http://www.aset.or.jp/>

CSM

OPTICAL TECHNOLOGY

Introduction



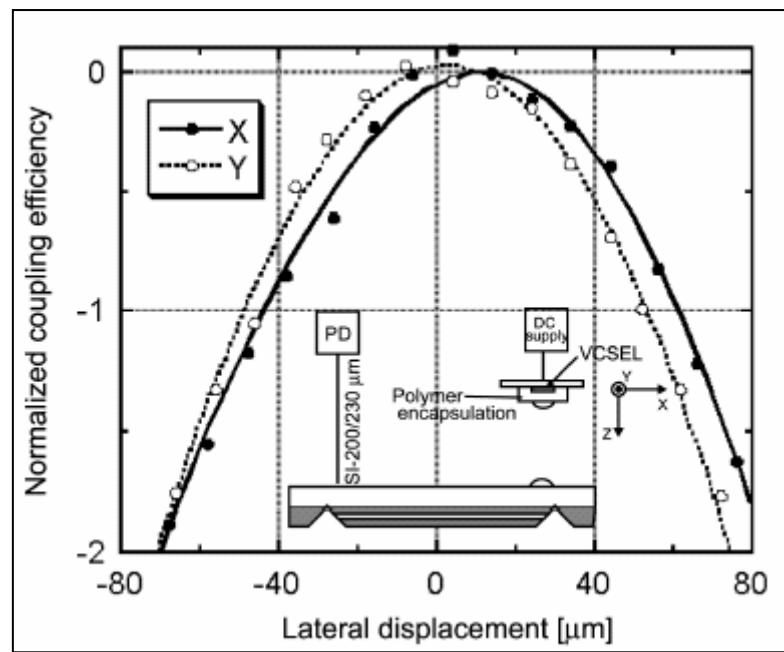
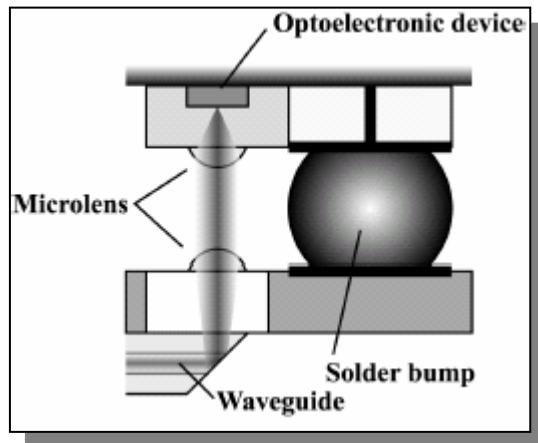
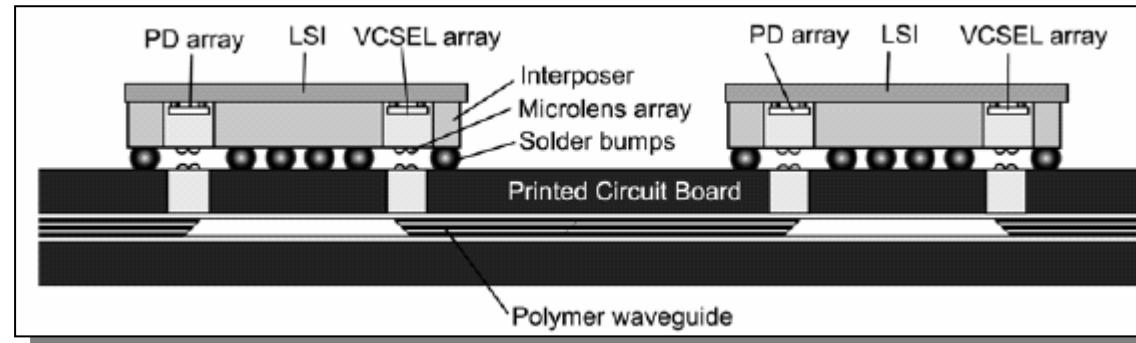
Ball pitch: 1.27 mm

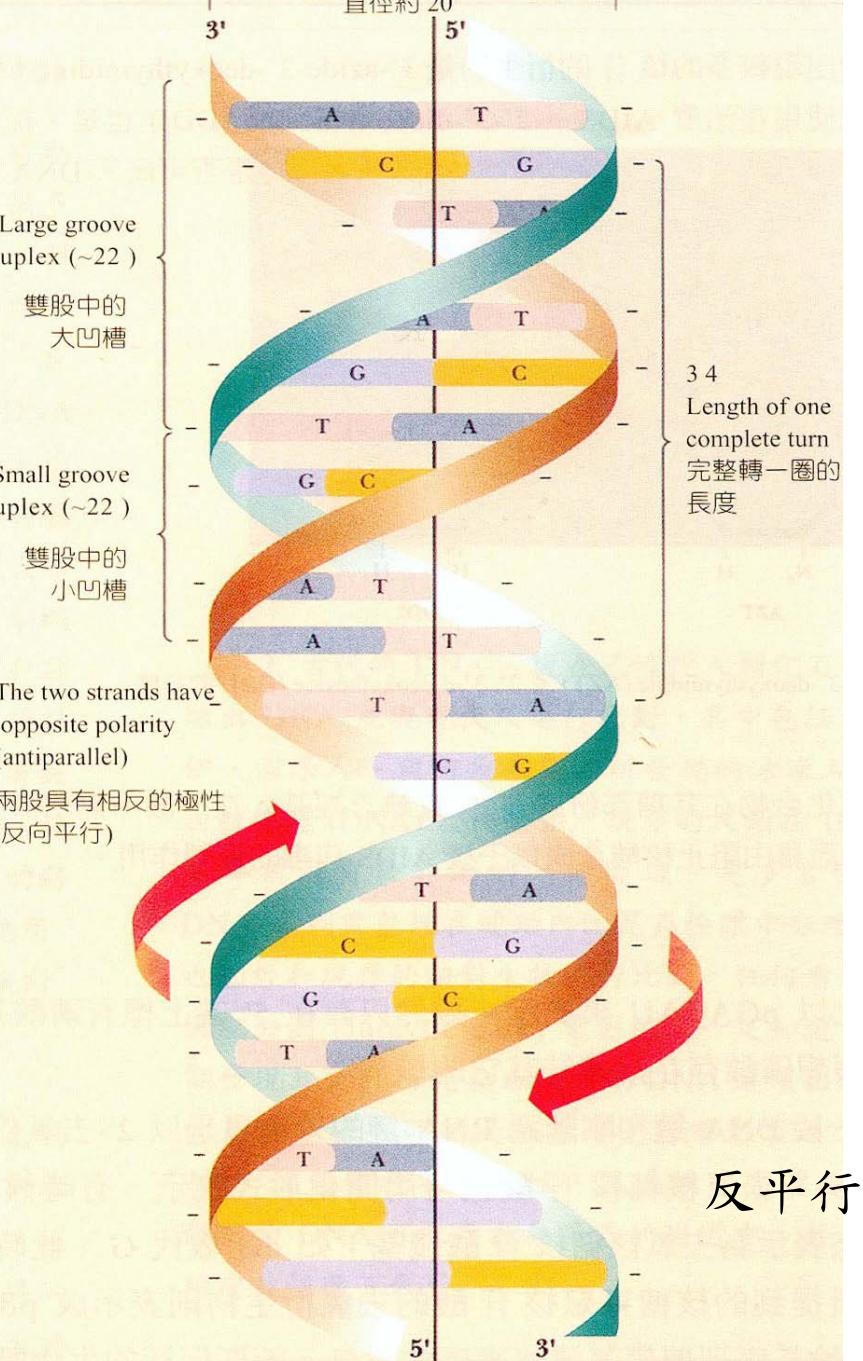
Out of consideration: **microlens**

reflective mirror

Literature Survey

2001 Ishii

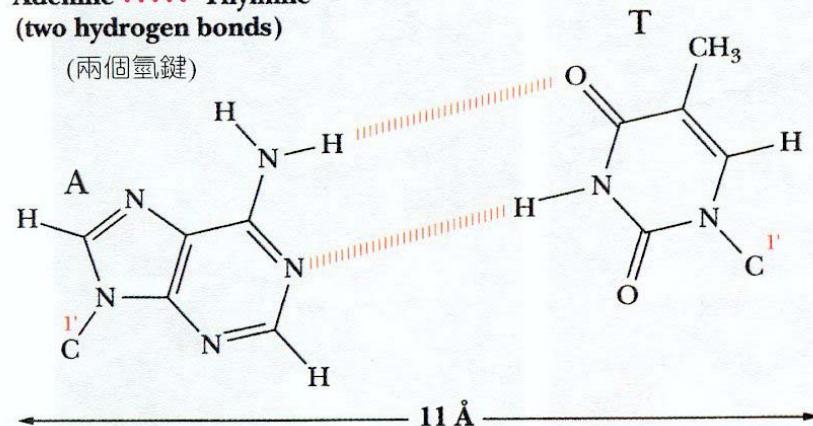




腺嘌呤 胸腺嘧啶

**Adenine :::: Thymine
(two hydrogen bonds)**

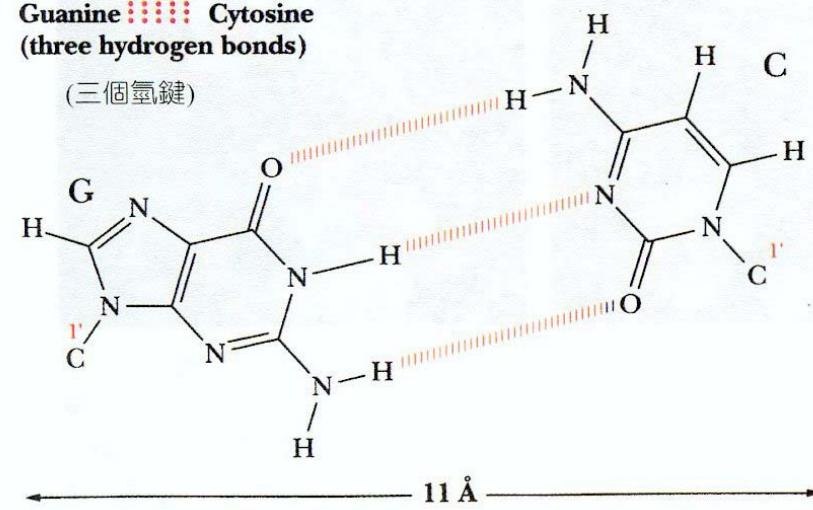
(兩個氫鍵)



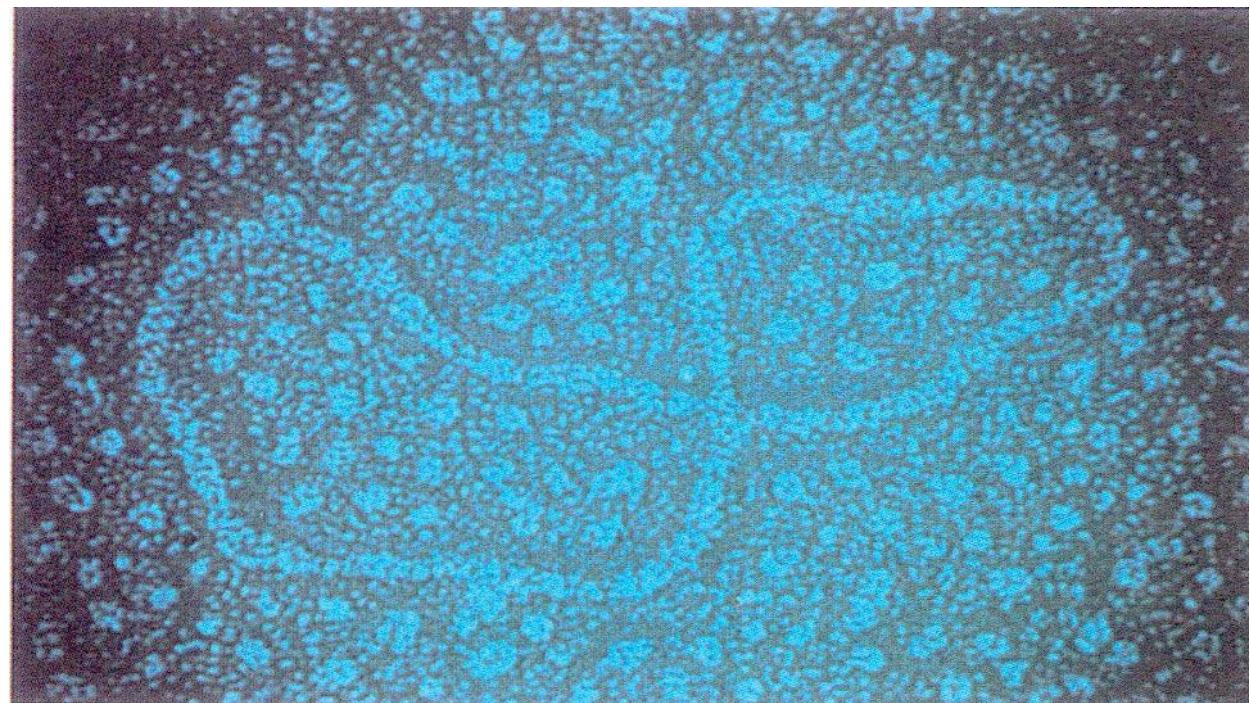
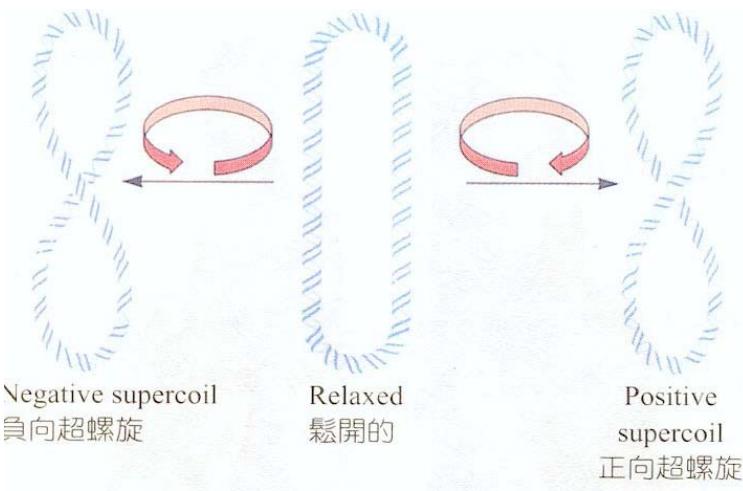
鳥嘌呤 胞嘧啶

**Guanine :::: Cytosine
(three hydrogen bonds)**

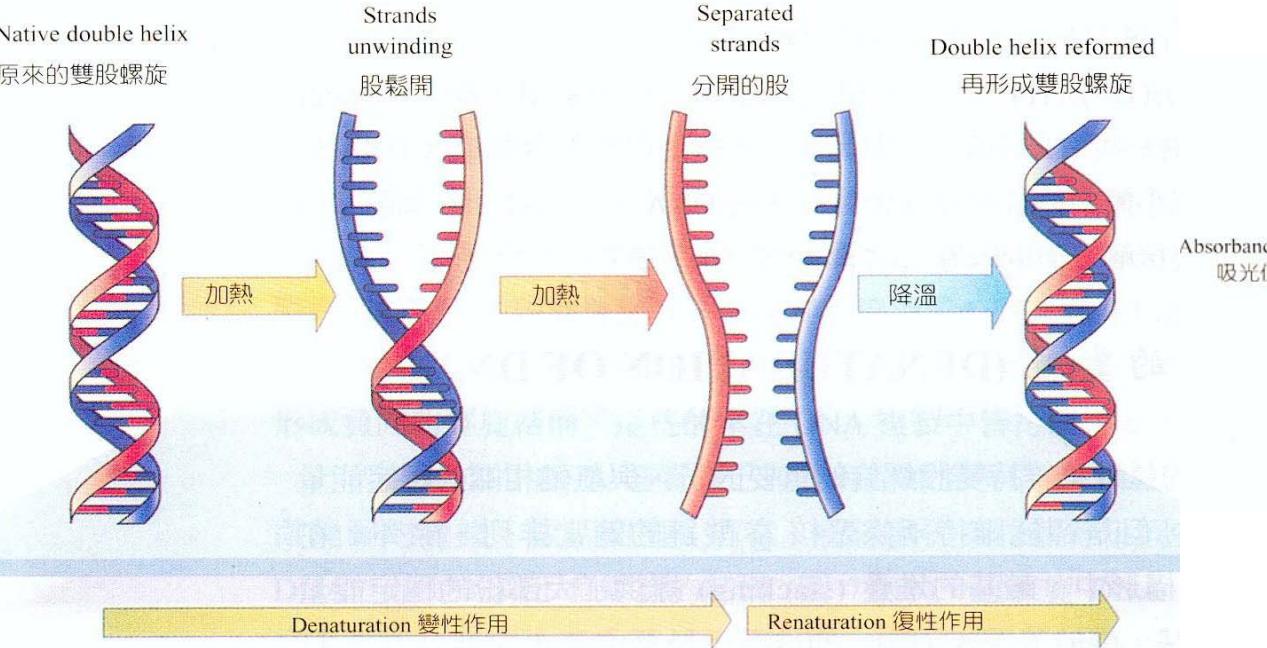
(三個氫鍵)



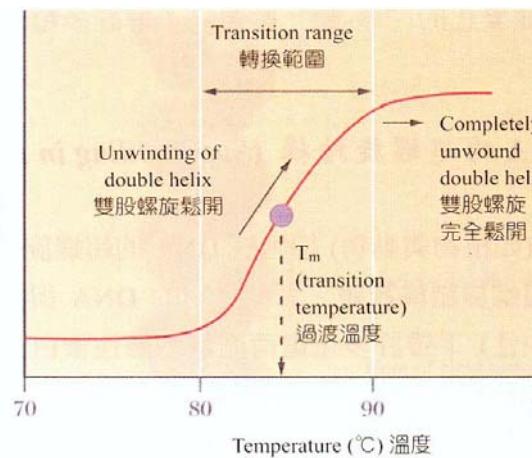
原核生物DNA 的超螺旋結構



DNA變性(Denaturation)



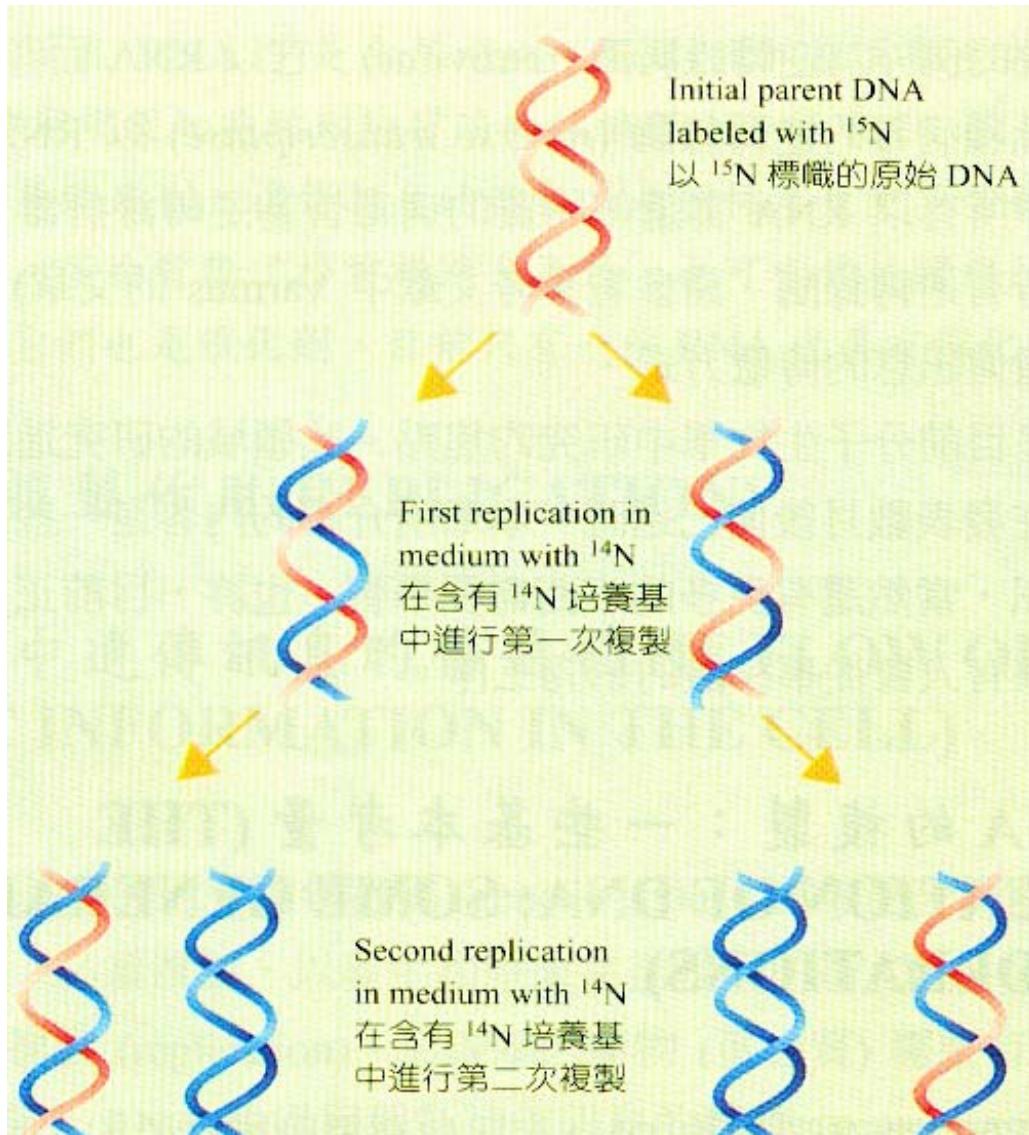
增色效應



$$\lambda = 260\text{nm}$$

CSML

半保留複製



1950年代

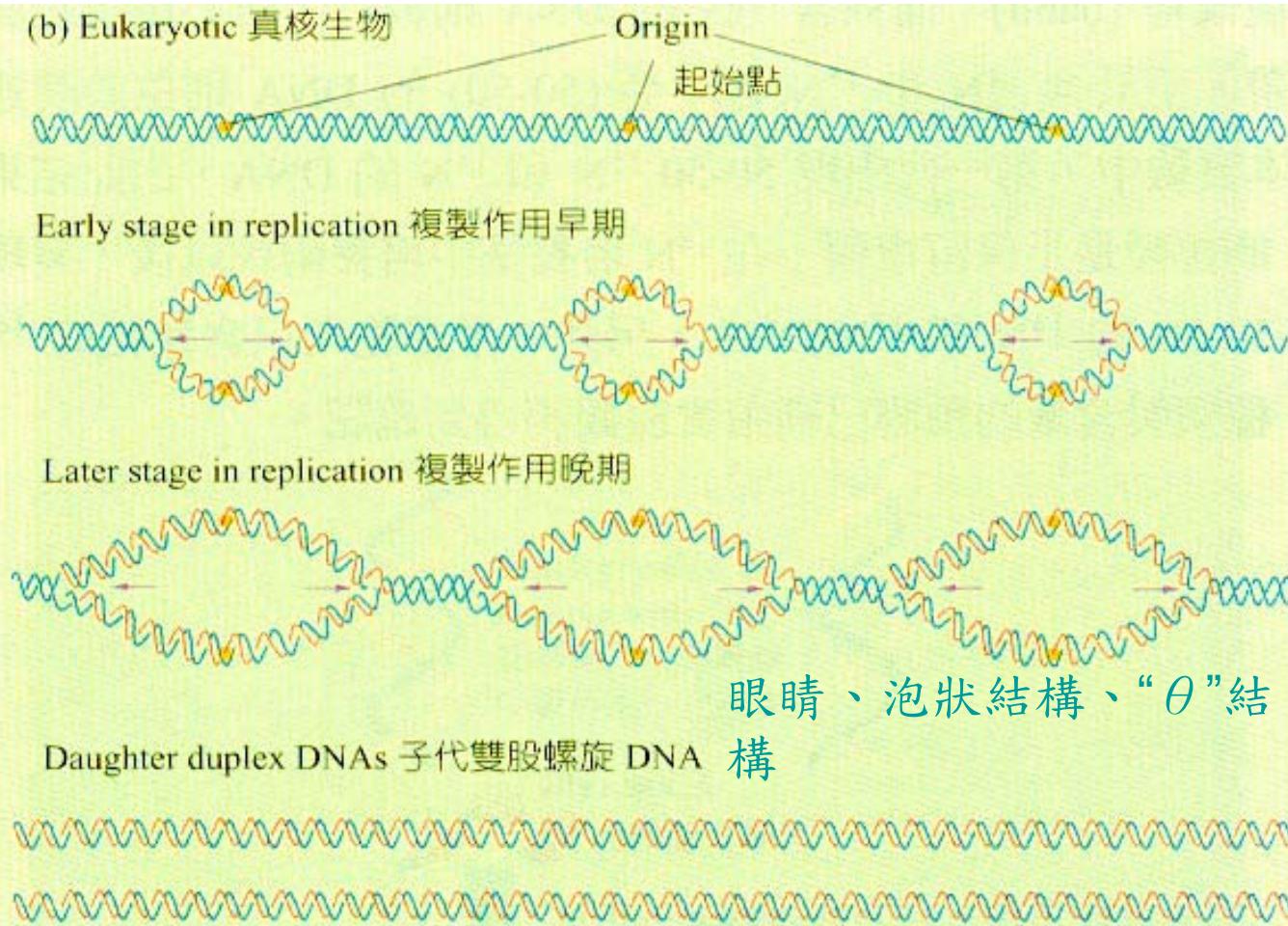
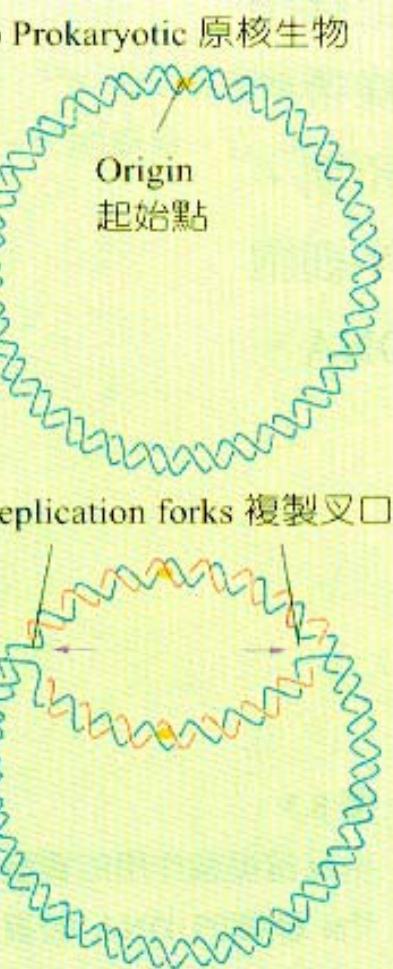
Meselson和Stahl

實驗證明。

密度 - 梯度離心法

CSML

雙向複製

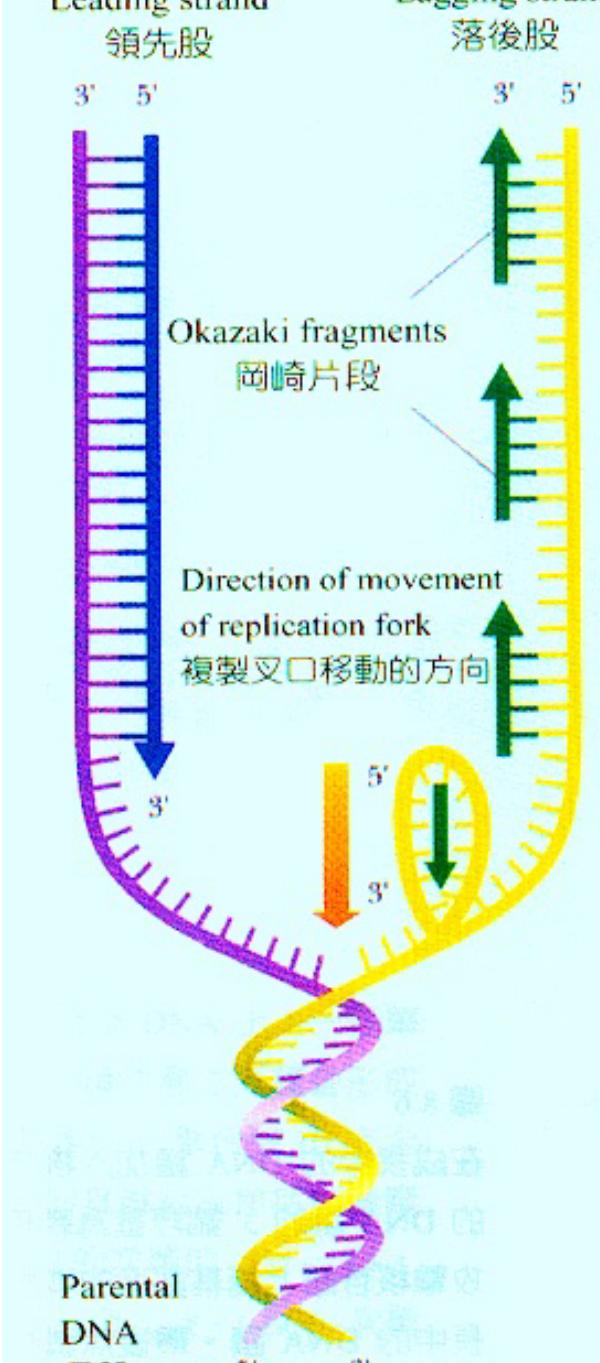


複製過程

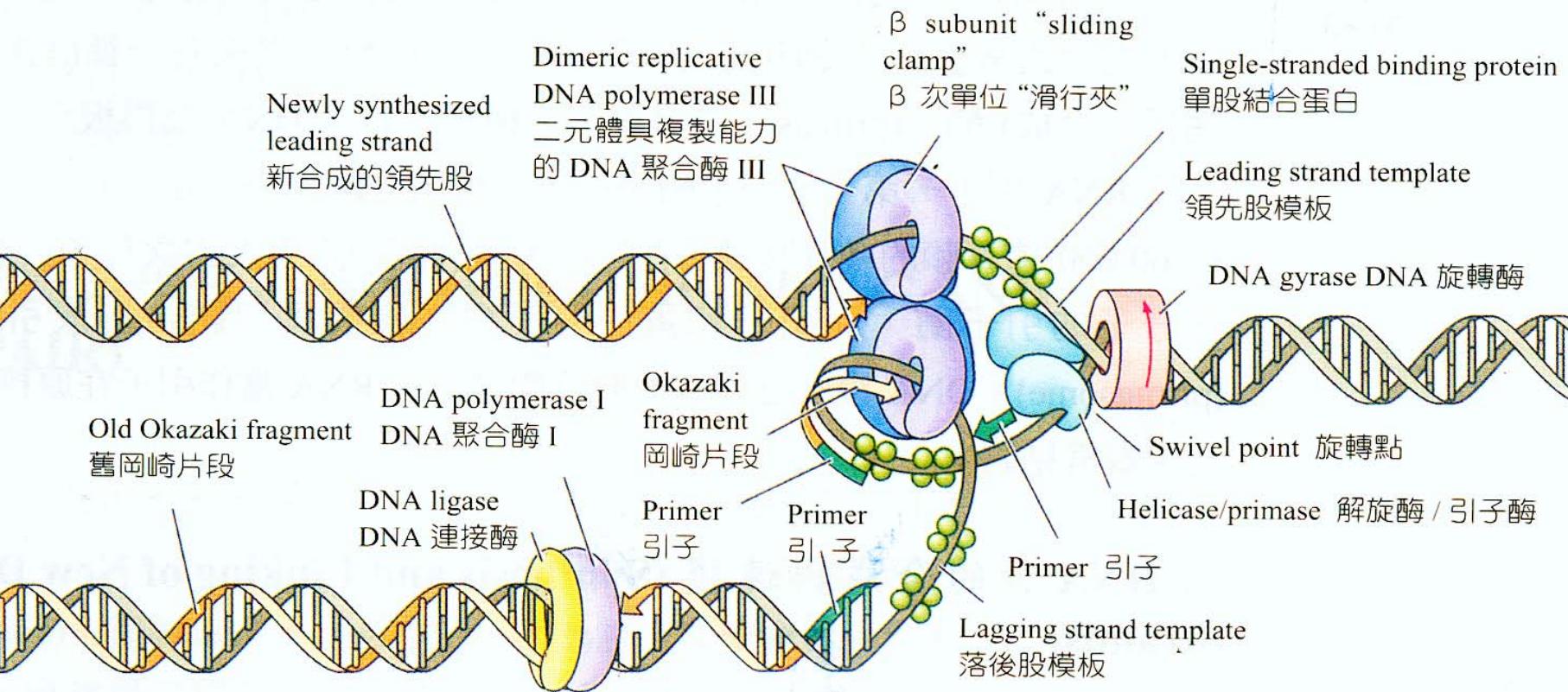
DNA的合成必須由 $5' \rightarrow 3'$

落後股(Lagging strand)由岡崎片段(1000-2000核苷酸長度)組成。

岡崎片段(Okazaki fragments)最後由DNA連接酶(DNA ligase)的酵素作用而連結起來。

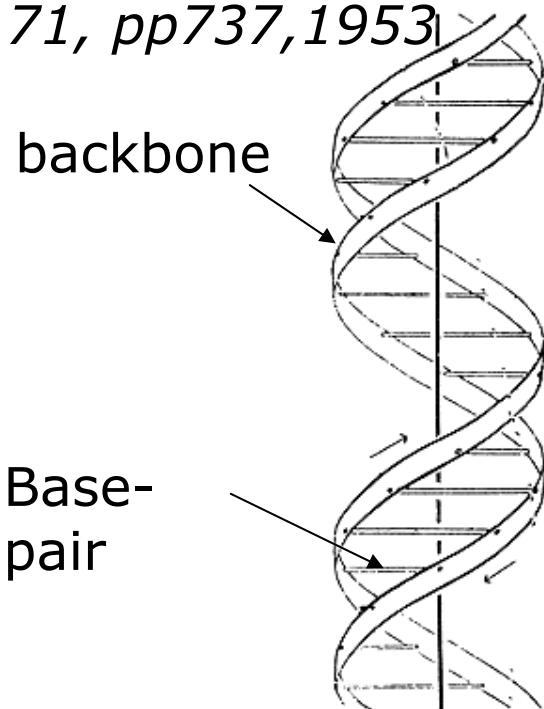


DNA複製需要的酵

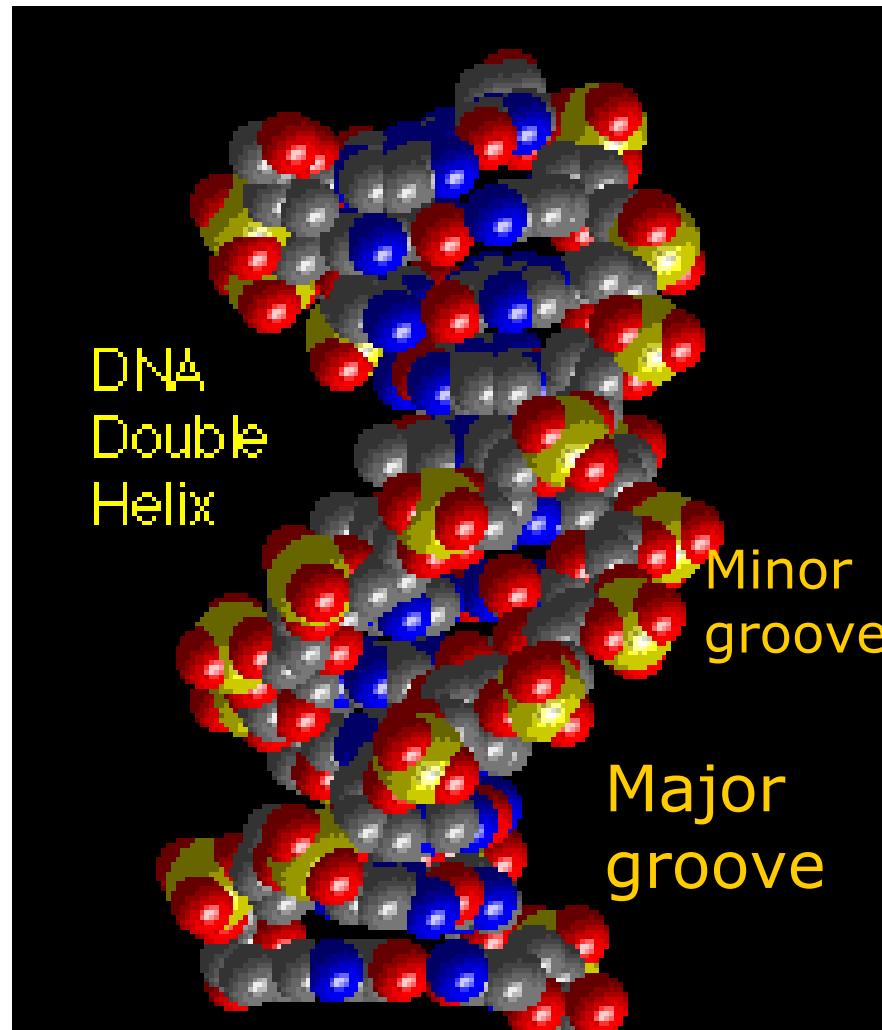


DNA Structure

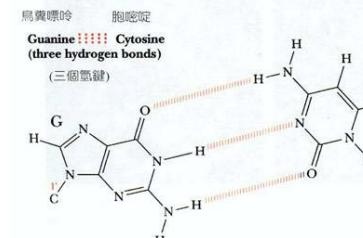
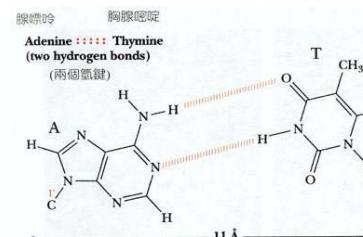
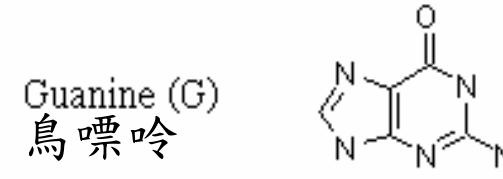
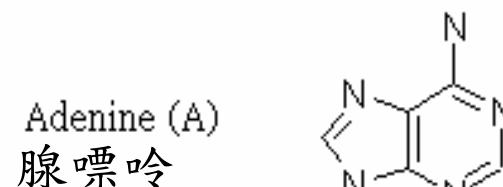
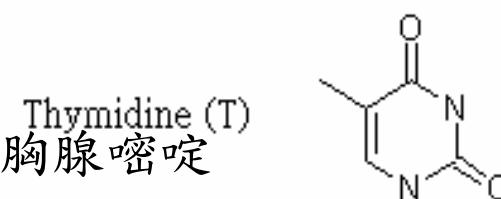
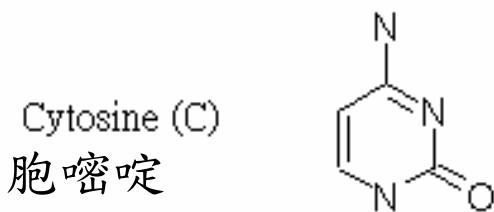
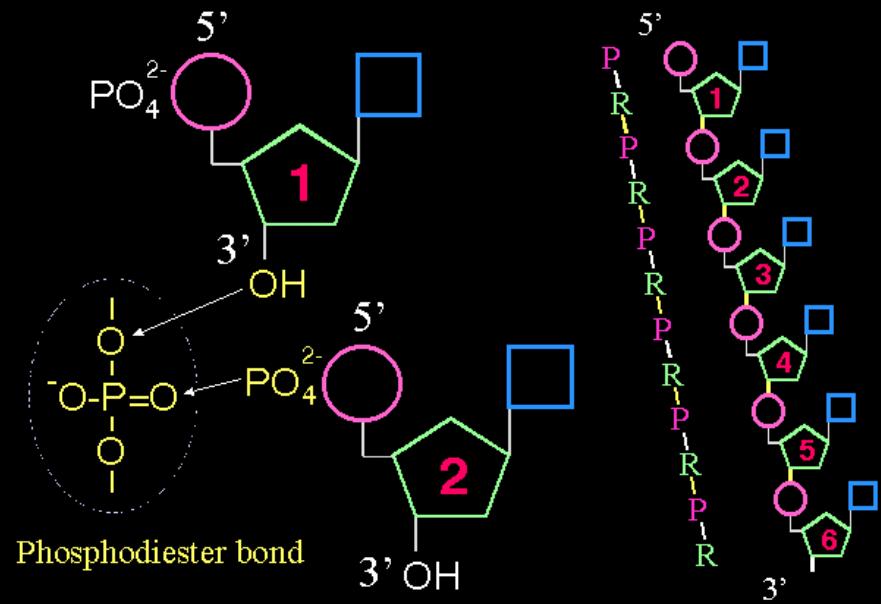
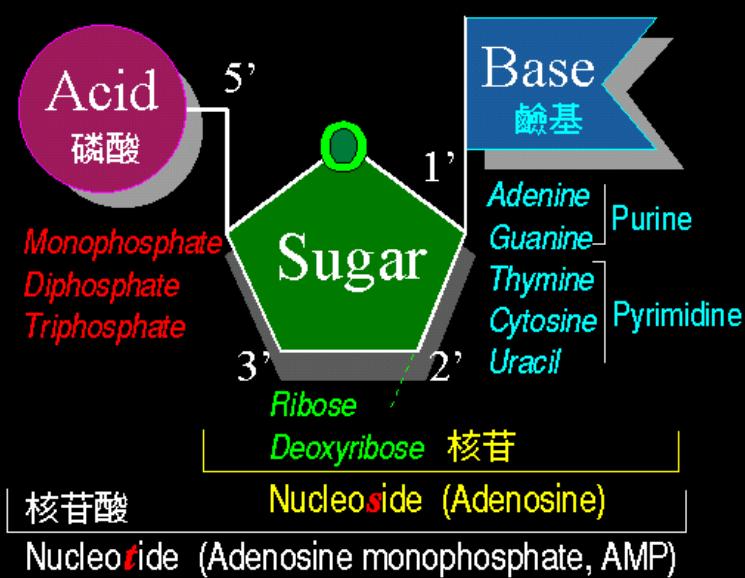
Watson & Crick's double helix
DNA proposed on *Nature*, vol
171, pp737, 1953



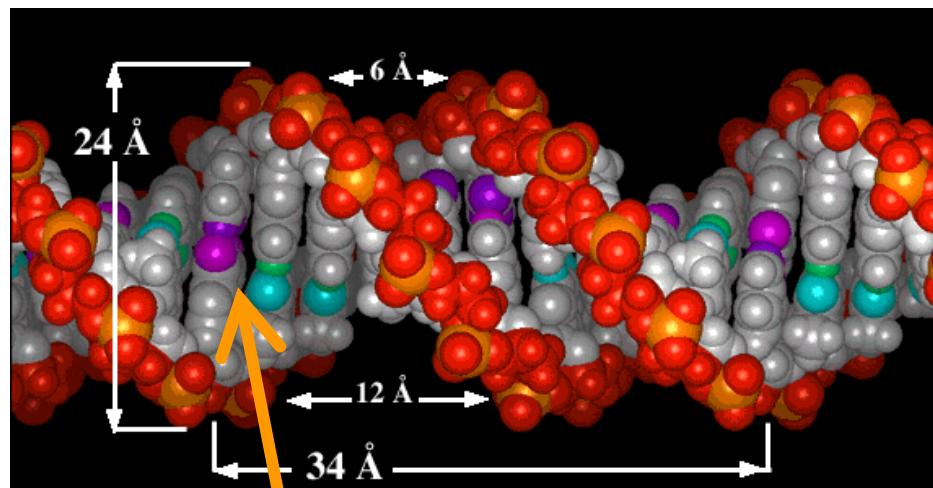
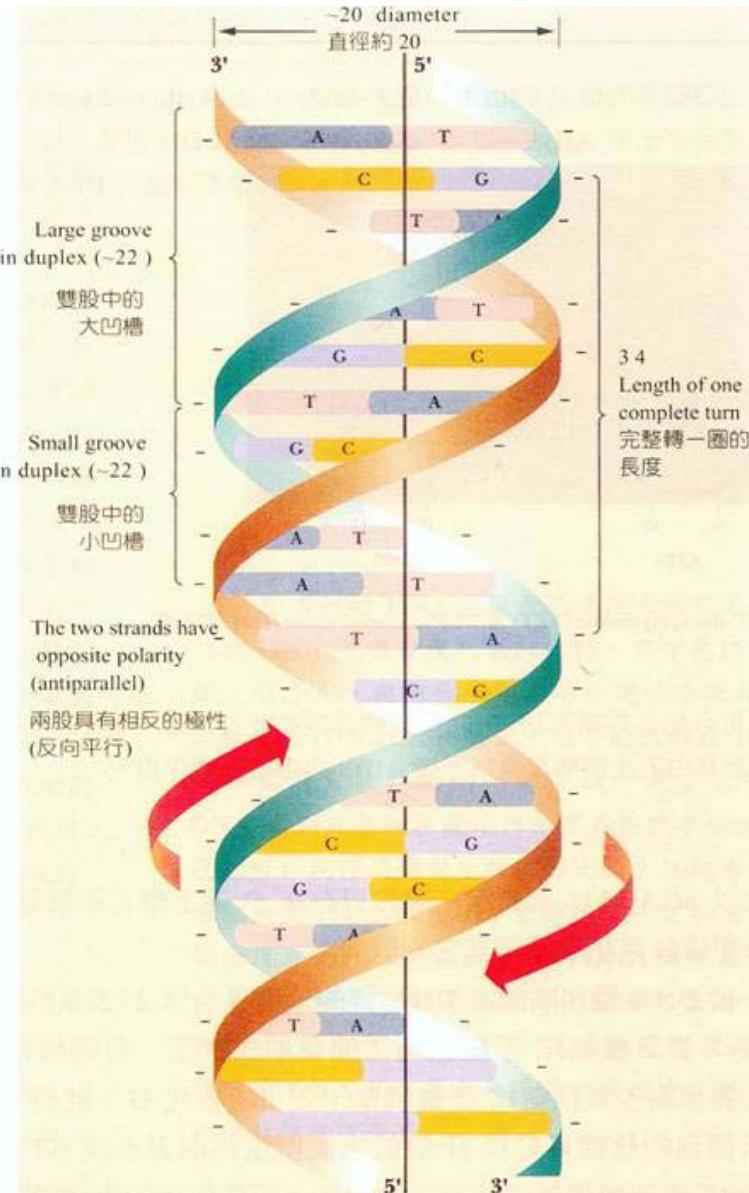
This figure is purely diagrammatic. The two ribbons symbolize the two phosphate-sugar chains, and the horizontal rods the pairs of bases holding the chains together. The vertical line marks the fibre axis.



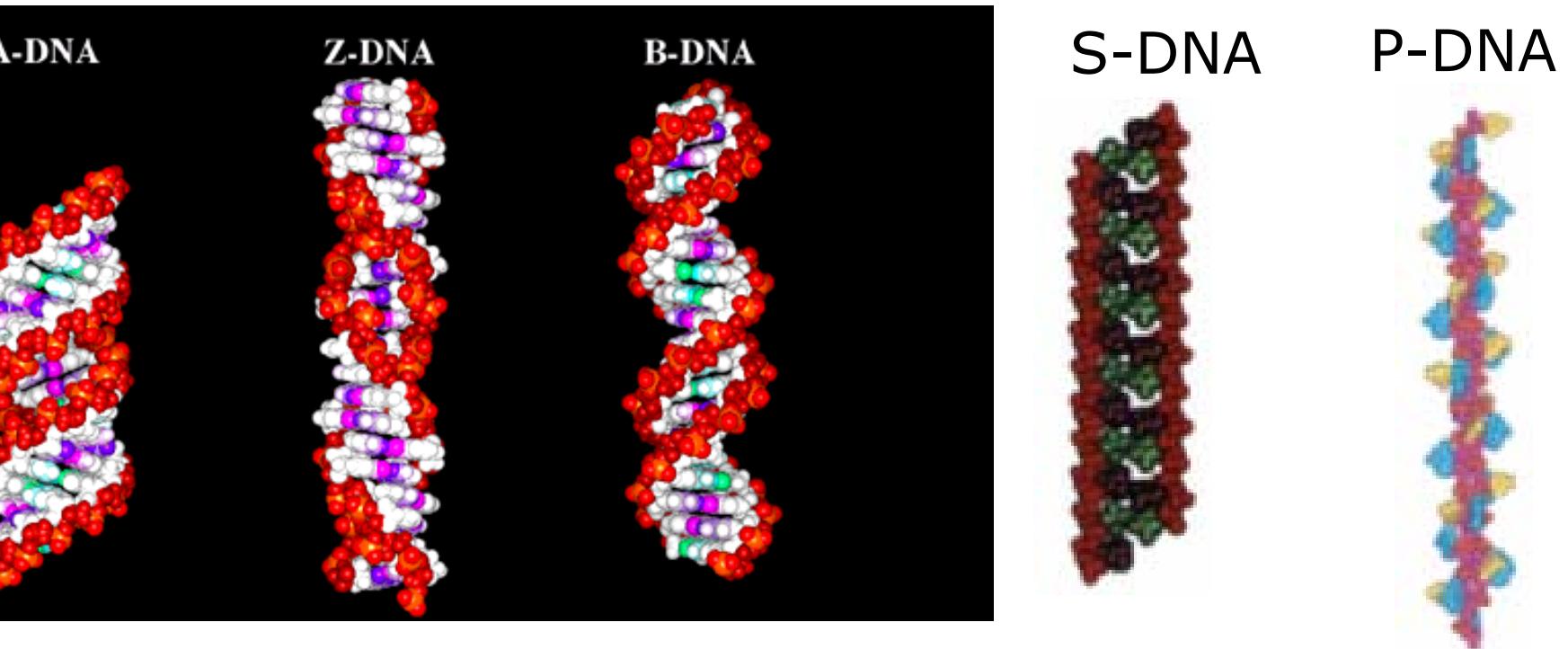
Chemical Composition of DNA



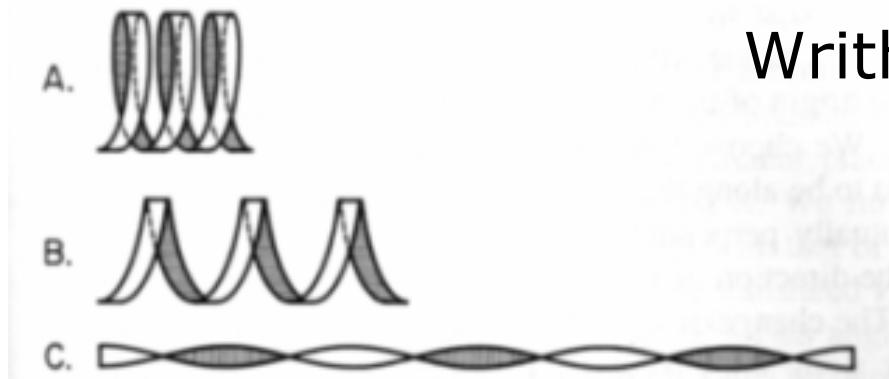
Geometry of DNA



DNA conformation



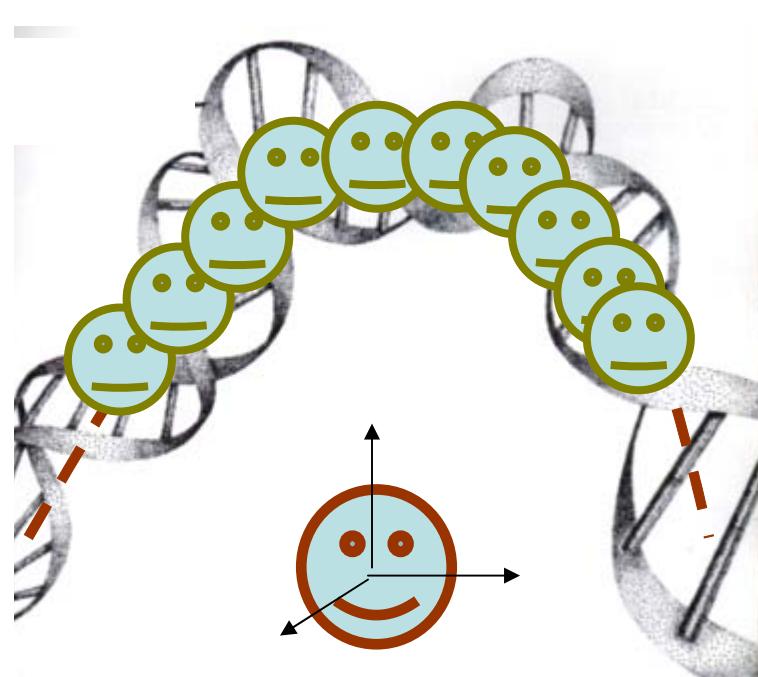
The linking Number-- Definition



Writhe=3, Twist=0



Writhe=0, Twist=3



Tw

Wr

$$L_k = Tw + Wr$$

Degree of Supercoiling (超螺旋度)

$$\sigma = \frac{L_k - L_{k_0}}{L_{k_0}}, \quad L_{k_0} \approx \frac{N_{bp}}{10.5}$$

σ : Degree of Supercoiling

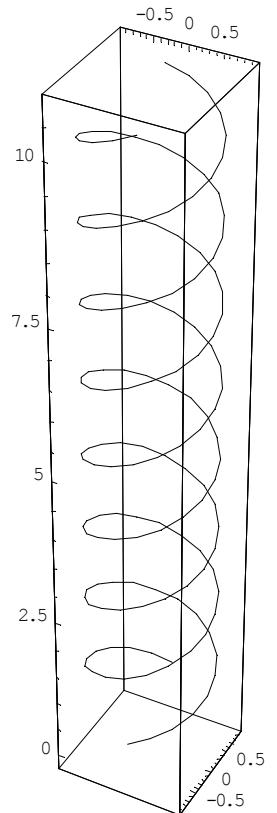
N_{bp} : Total Number of base-pairs

if

$\sigma > 0$, overtwisted

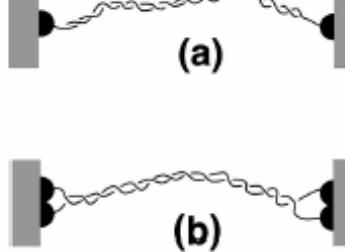
$\sigma < 0$, undertwisted

usually, B-type DNA $\sigma \approx -0.05$ (in vivo)

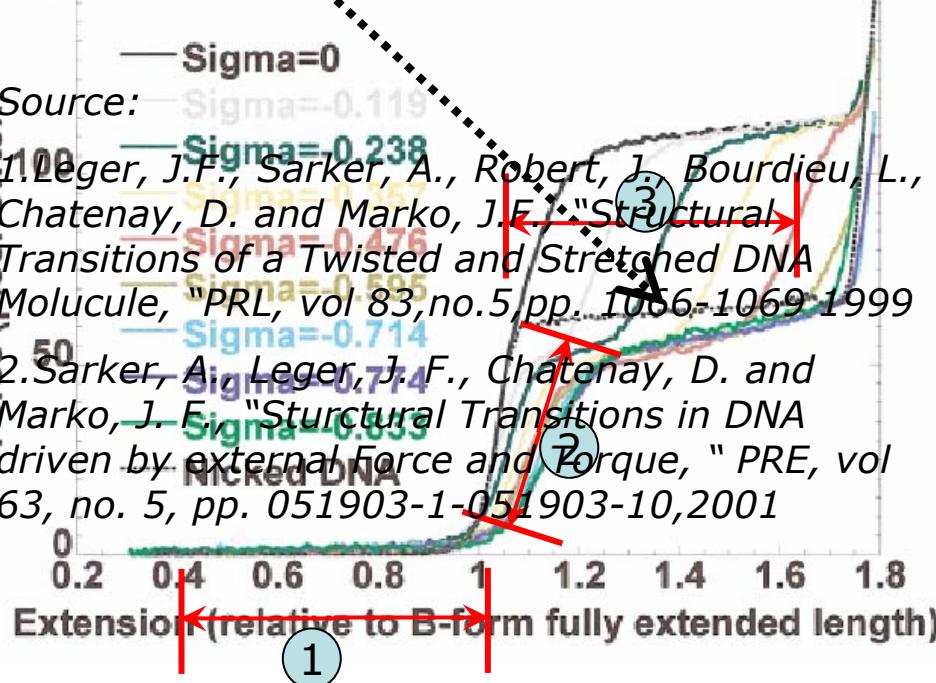


(a)

DNA Strength Diagram

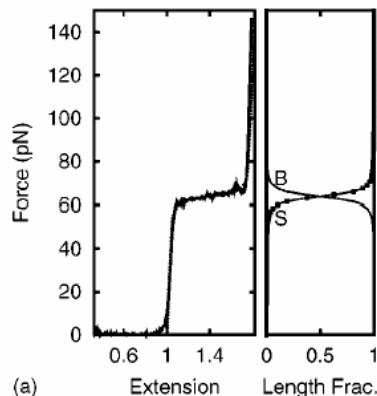


Nicked DNA(ssDNA)



Sample:

dsDNA, 44kb ~
 $14.96 \mu\text{m}$, $L_{k0} = T_{w0} \sim 4200$ (44kb/10.5 ~ 4190)

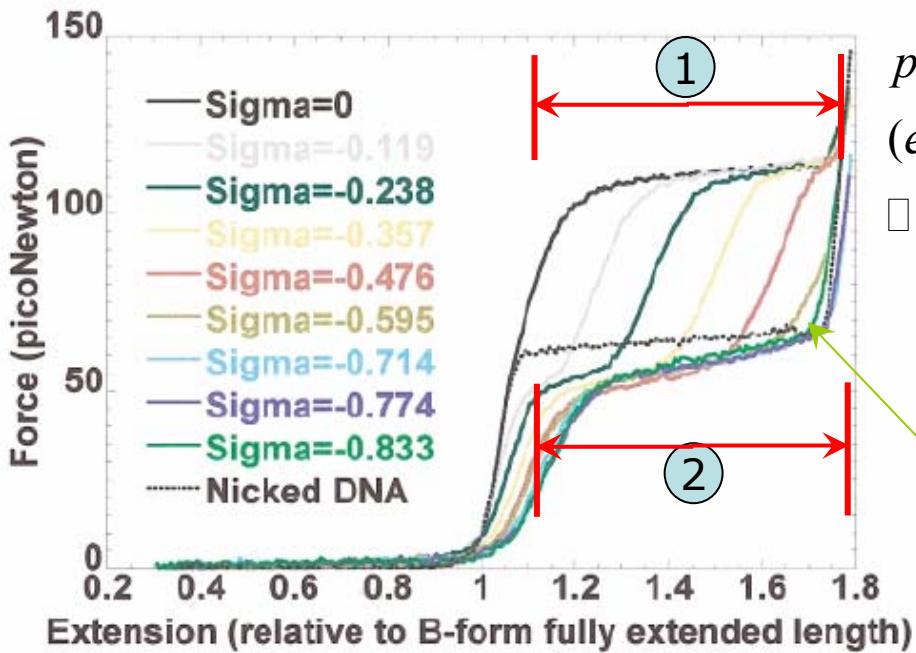


- ①: 0~10pN, to remove bending from random coil
- ②: 10~65pN, Almost linear stretching elastic constant
- ③: S-DNA, 65pN plateau, 1.7 times longer than B-DNA

$$\text{from } \sigma = \frac{L_k - L_{k0}}{L_{k0}}, L_{k0} = N_{bp} / 10.5$$

$$\text{bps / turn} = \frac{10.5}{1 + \sigma} \approx 37.5$$

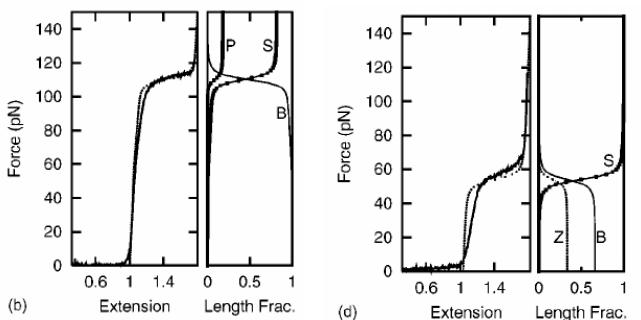
Under twisted



pitch per turn :

$$(\text{extension}) * (0.34\text{nm}) * (37.5)$$

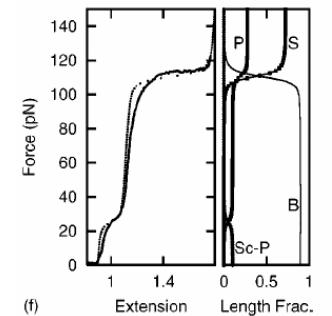
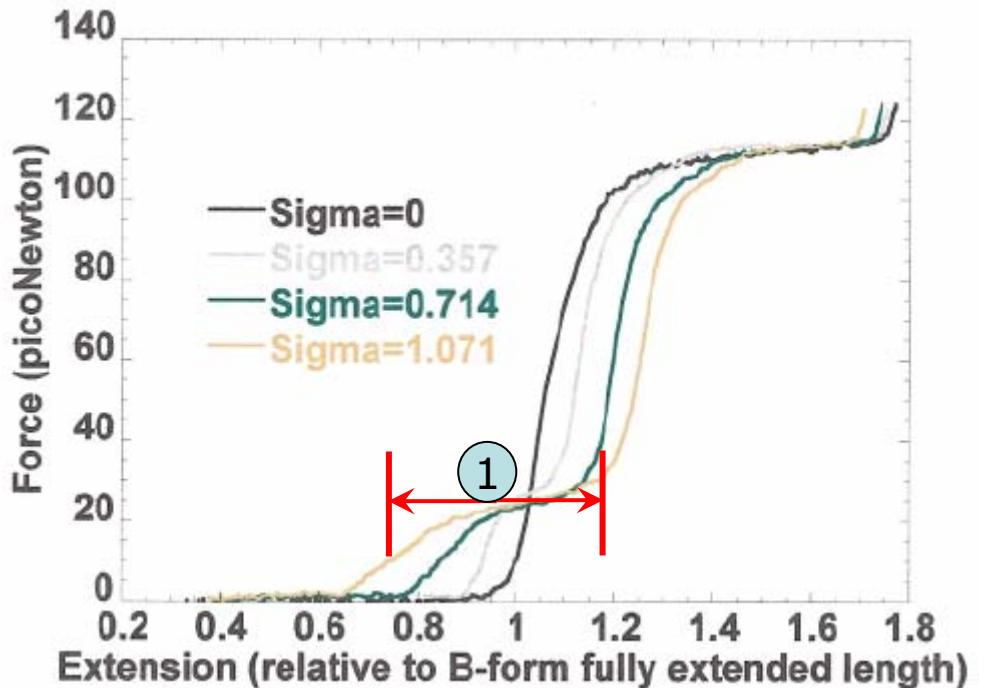
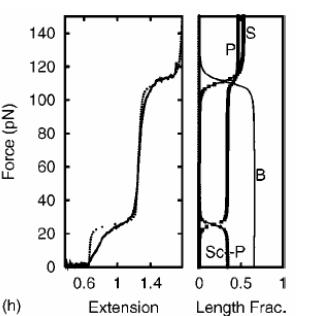
□ 21.675nm



- ①: $\sigma = 0$, unnicked DNA, 110pN plateau appears(S+P Type)
- ②: at $\sigma = -0.1$, $\sim 50\text{pN}$ plateau appears
- ③: at $\sigma = -0.72 \pm 0.05$, the 110pN plateau disappear.

Def. S-DNA, pitch per turn $\sim 22\text{nm}$, 37.5 bps/turn

Over Twisted

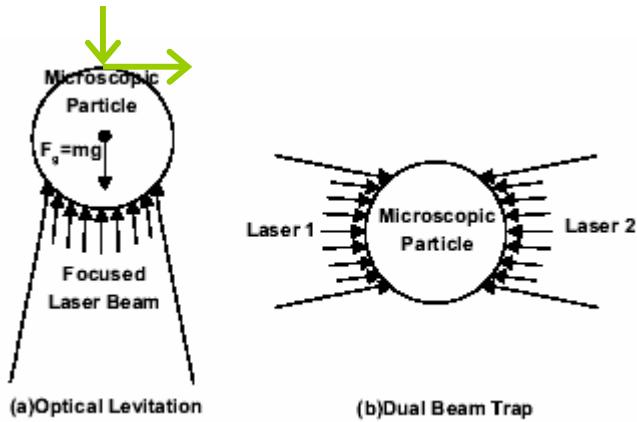

 $\sigma = 0.357$

 $\sigma = 1.071$

1: A new plateau at 25 pN



Principle of Optical Trap

- We could apply force on micro-particle by optical pressure, and trap and control the micro-particle.



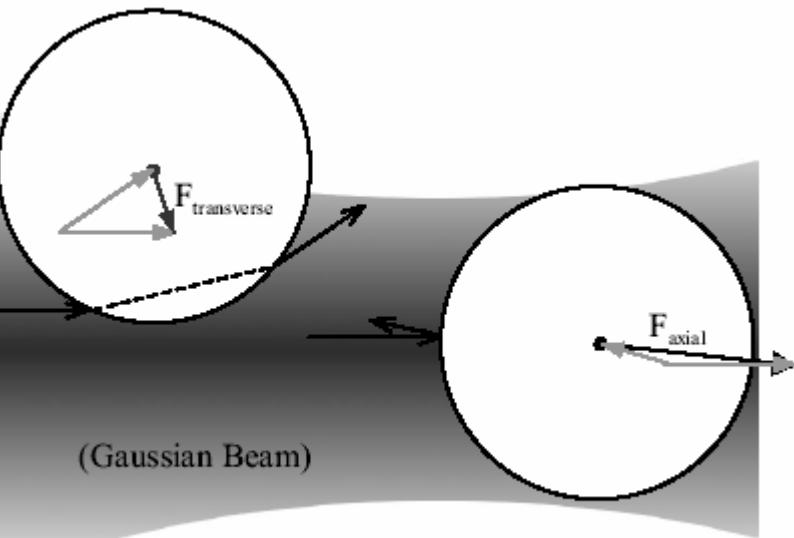
- Single Beam, Highly focus, large solid angle → single beam optical trap
- Gradient Force: orthogonal to light ; Scattering Force: parallel to light

Brief History of Optical Trap

- A. Einstein: Photon Model
- A. Ashkin(1969): Optical Pressure experiment
- A. Ashkin(1970-1980): first laser trap (Ar Laser)
- A. Ashkin & S. Chu (1986): Single Beam Optical Tweezers
- A. Ashkin (1987): manipulate cell by YAG laser (1064nm)
- S. Chu (1997): Nobel prize: laser cooling

Preliminary Theory Study: RO Model

- RO (Ray-Optics Model)
- Describe optical trap by geometric optic and momentum change of photon
- micro-particle diameter larger than wave length



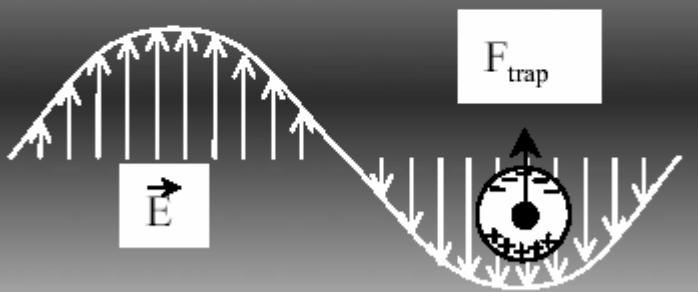
Gradient force:
refract photon while laser enter micro-particle,
which cause momentum change of photon.
Base on Newton Mechanics, there are force act
on microparticle

Scattering Force:
Part of photon reflex upon micro-particle, which
cause axial force

Preliminary Theory Study: EM Model

- EM model: Electromagnetics model
- Base on the EM theory and micro-particle being polarize
- micro-particle diameter smaller than wave length

Gaussian Beam



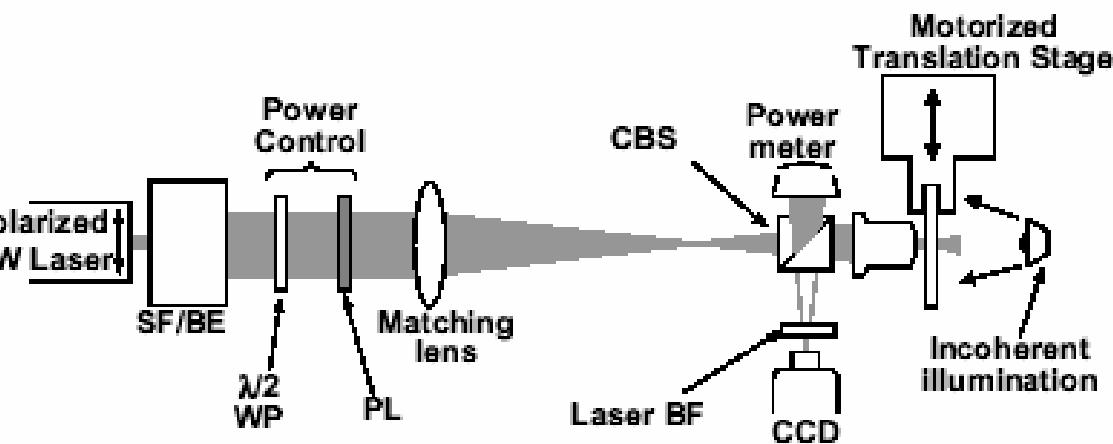
Gradient force:

As the laser polarizes the object, the object experiences a force in the gradient of the electric field

Scattering Force:

Light being reflected or absorbed by the particle
The scattering force is proportional to the optical intensity.

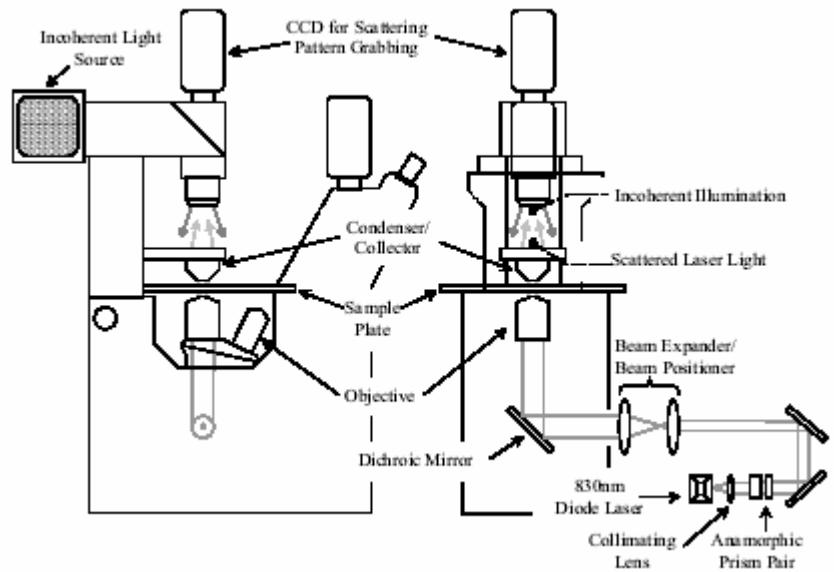
Basic Optical Trap Instrument



Optical tweezers typically use light at wavelengths of 0.7~1.06 um and 25 to 500 mW

- CW laser
- SF(Spatial Filtering)
濾波
- BE(Beam Expanding)
擴束
- WP: Half Wave Plate
- PL: Polarizer
- Laser BF: Laser Blocking Filtering

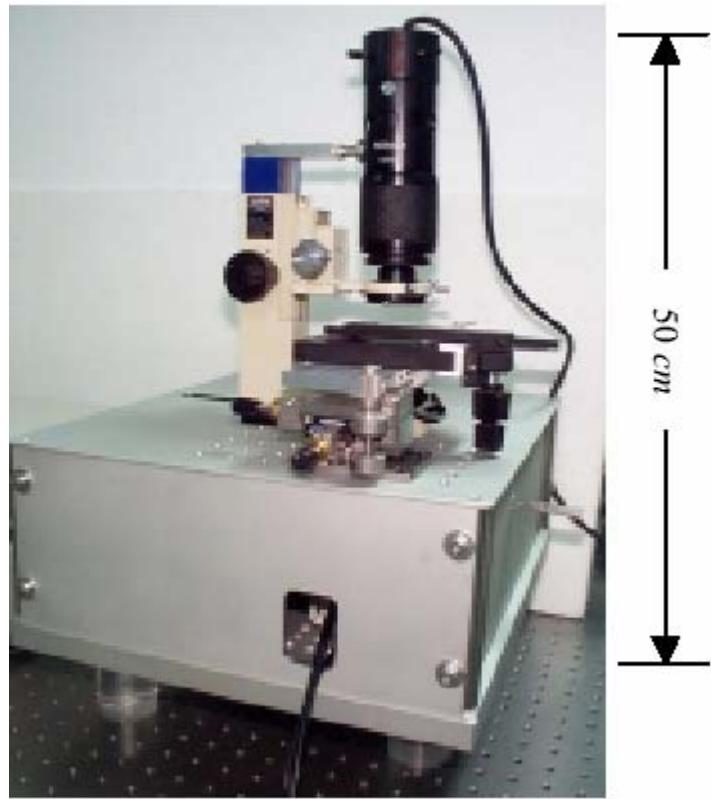
Optical Trap Instrument around TW Univ.



東華大學、電機系、邱爾德教授

陽明大學、微免所、林奇宏教授

Optical Trap Instrument around TW Univ.



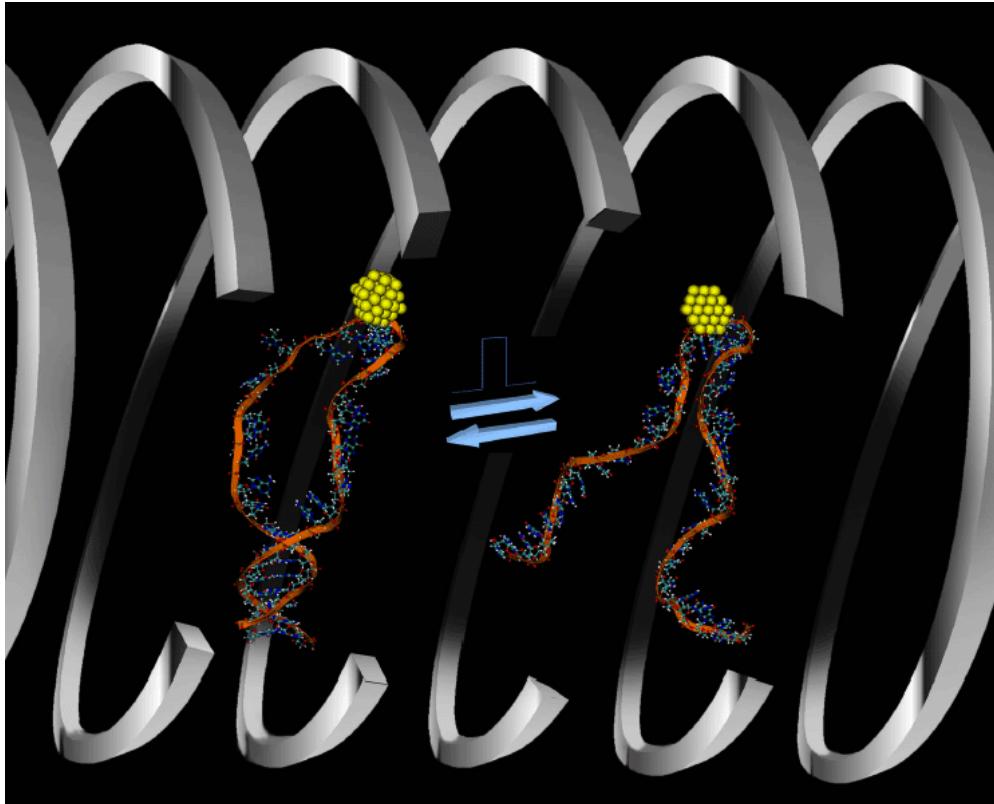
交通大学、電物系、徐琅教授

Remote electronic control of DNA hybridization through inductive coupling to an attached metal nanocrystal antennas

Author: Hamod,K, Schwartz,J.J., Santos, A.T.,
Zhang, S. and Jacobson, J.M.
(MIT Media Lab,US)

Journal: Nature, vol415, pp. 152-155
Date: 10-Jan-02'

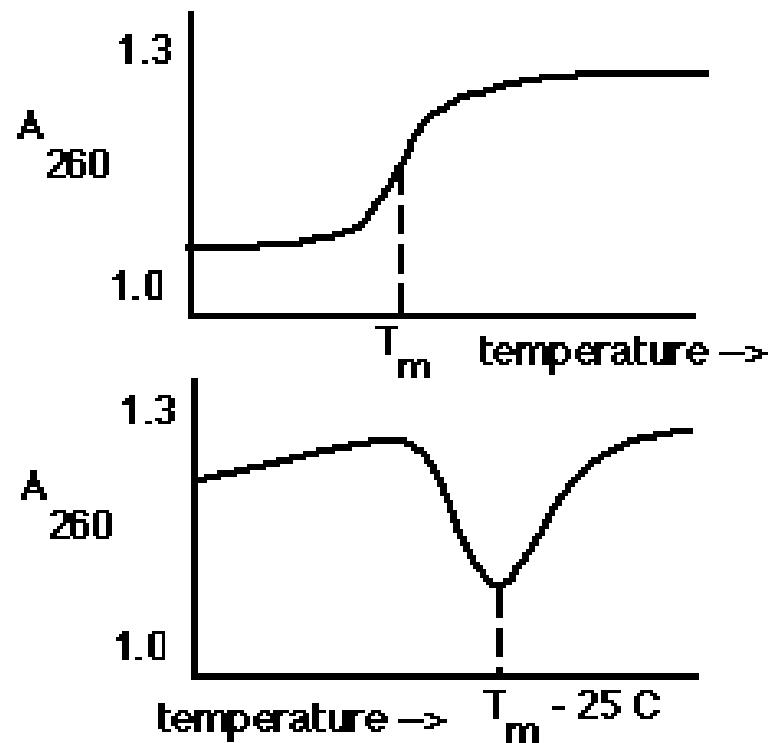
Hybridization by Antenna/Heat



Inductive coupling of a **RFMF** to metal convalency link to DNA.

Inductive coupling to the nanocrystal increase the **local temperature** of the bound DNA.

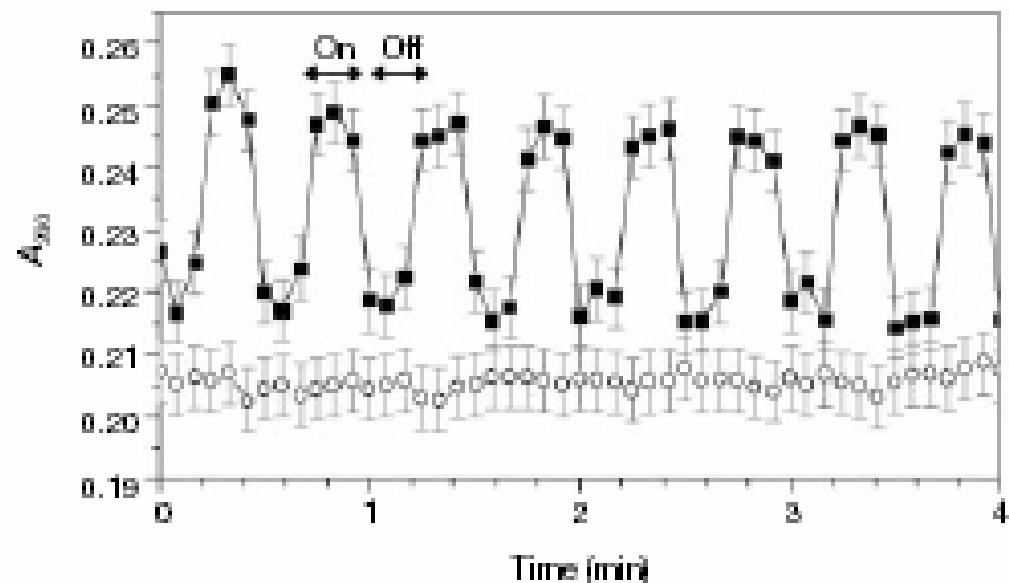
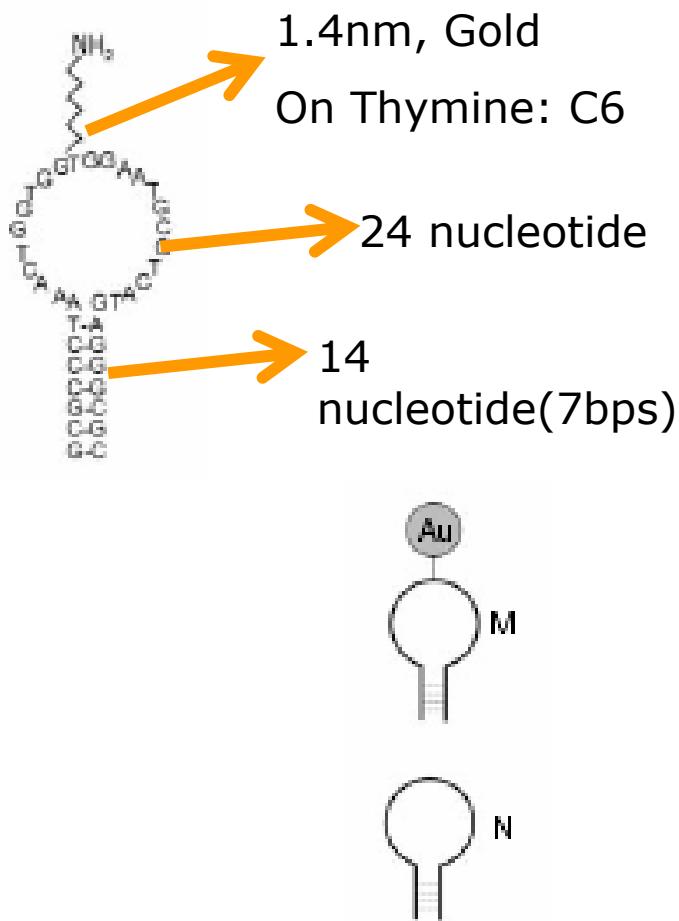
Hyperchromicity/DNA optically absorbance



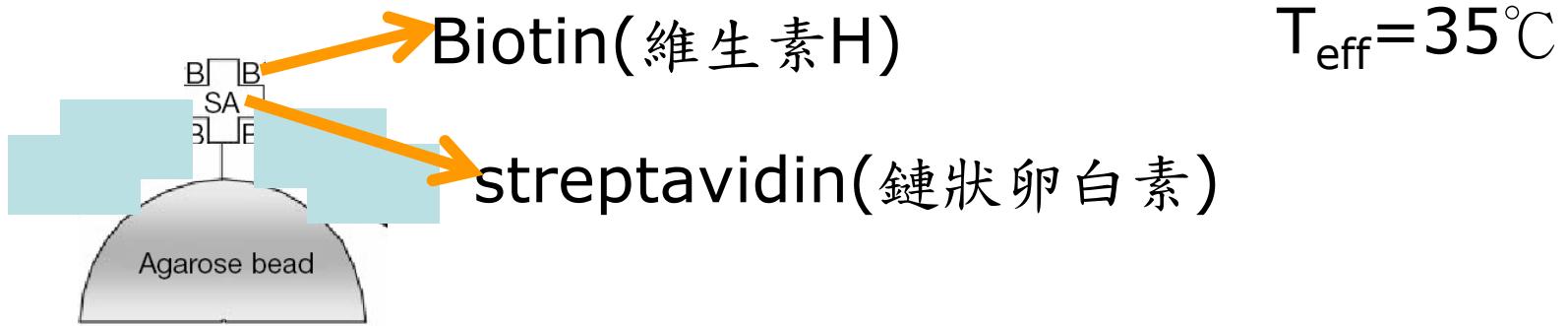
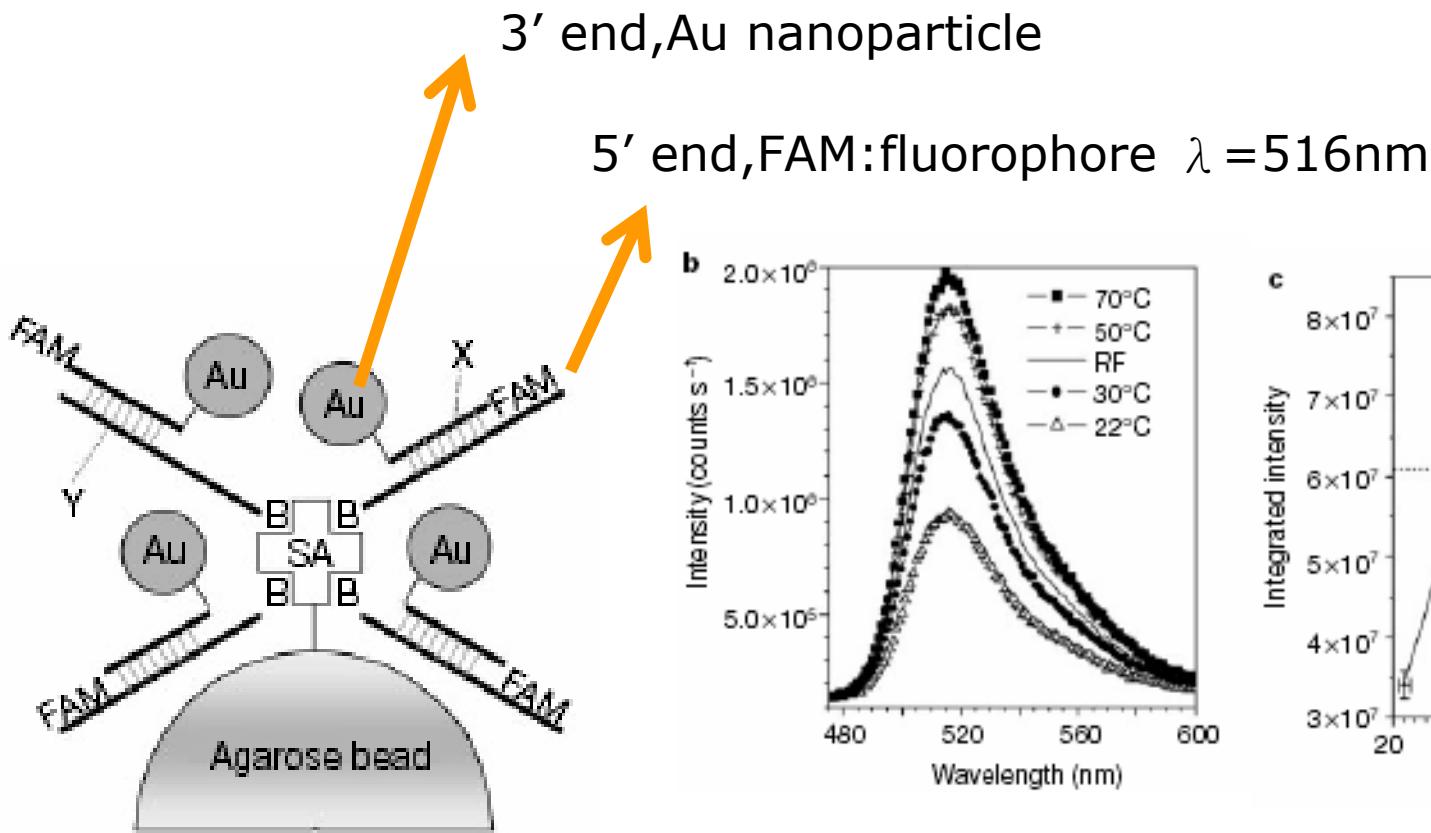
The absorbance of DNA at 260 nm (the absorption maximum) was followed as the DNA was slowly heated.

The hypochromicity was maximal about 25 C below the Tm.

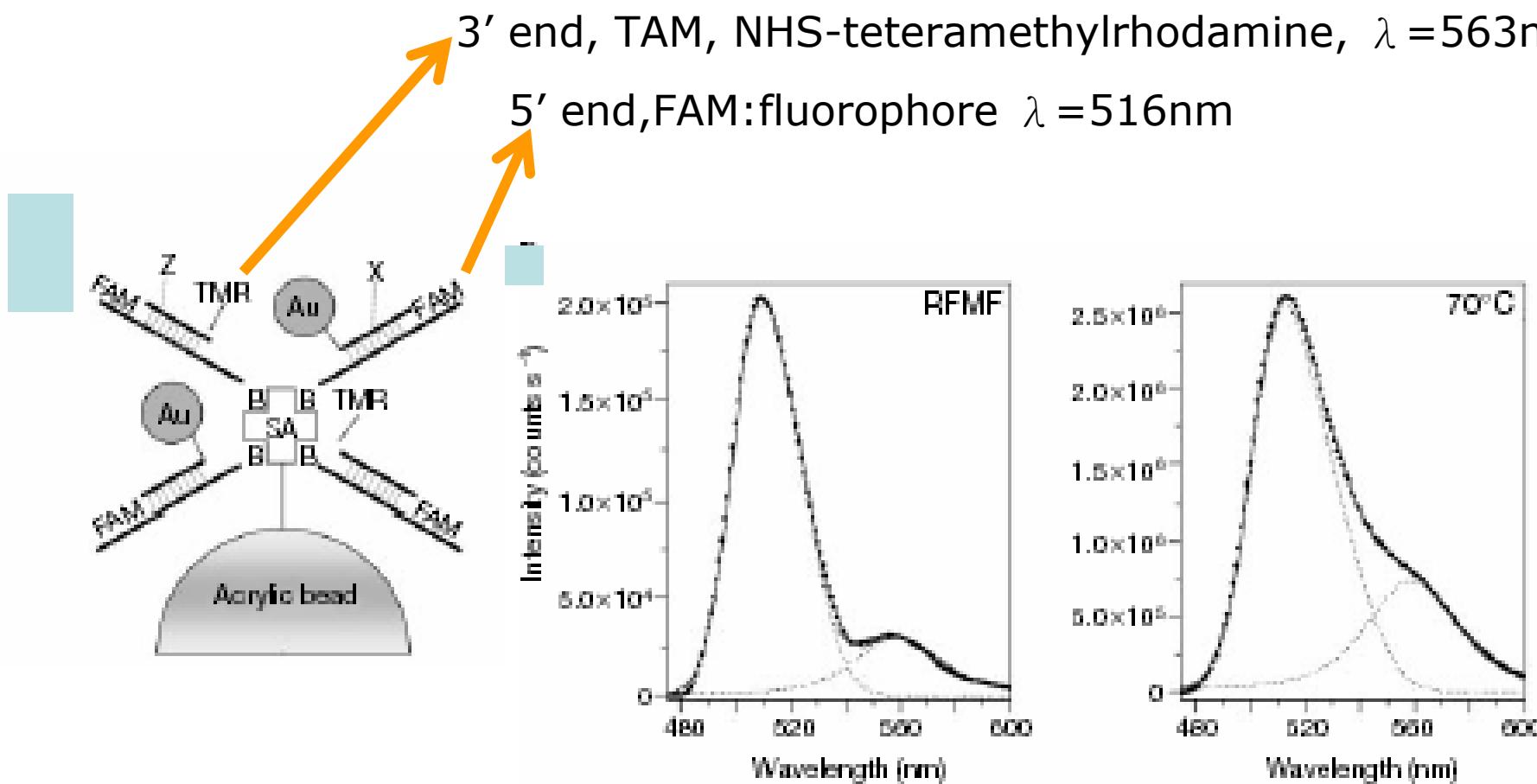
“Antenna” Design



Effective Temp.

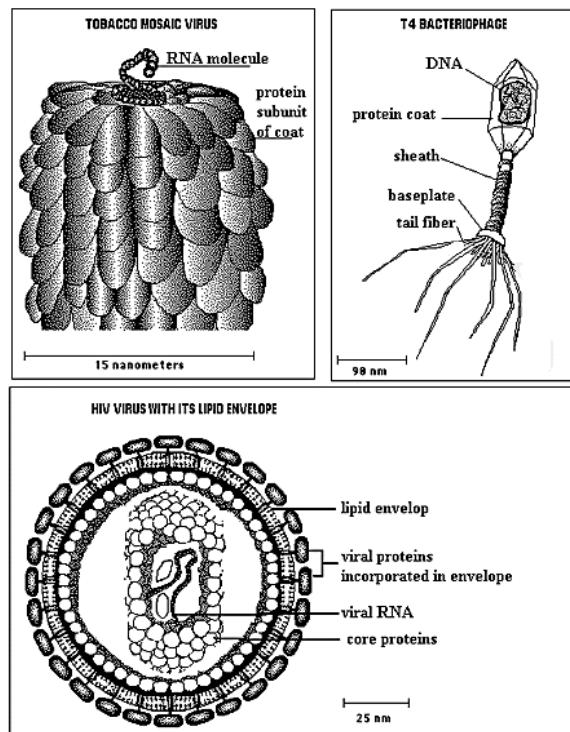
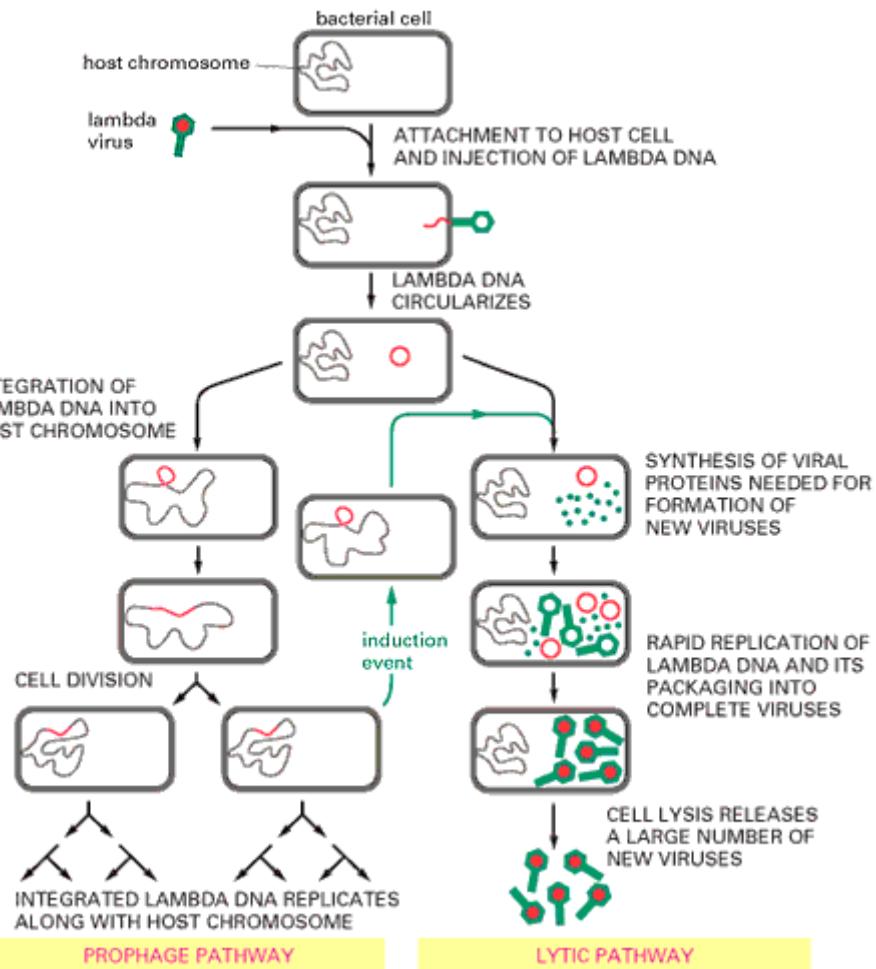


Selectivity



DNA Paper Review: DNA Packaged by Phage

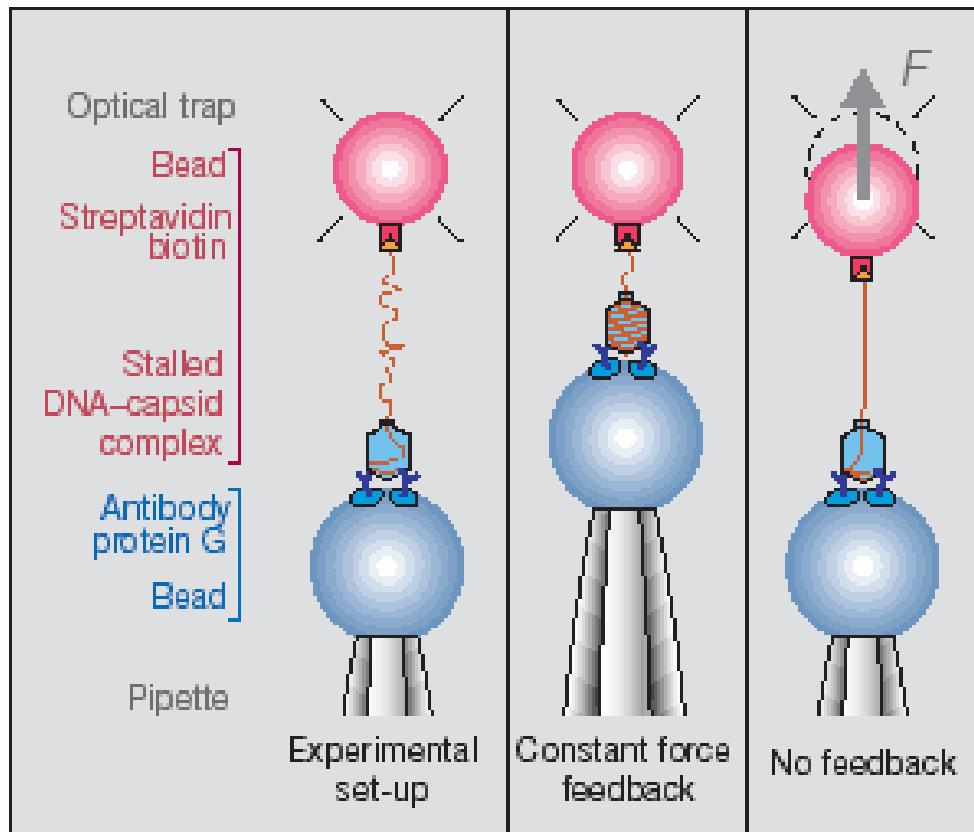
Phage &



Bacteriophage ϕ 29 study

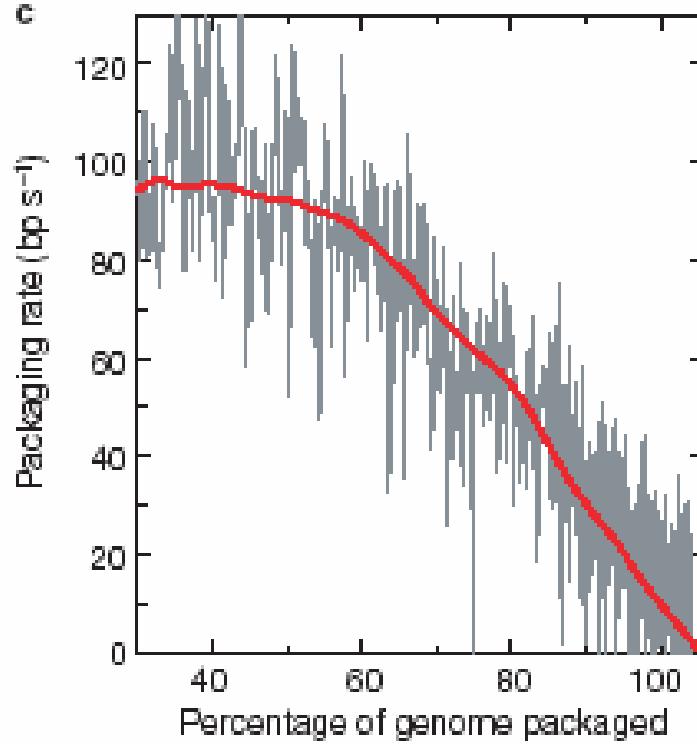
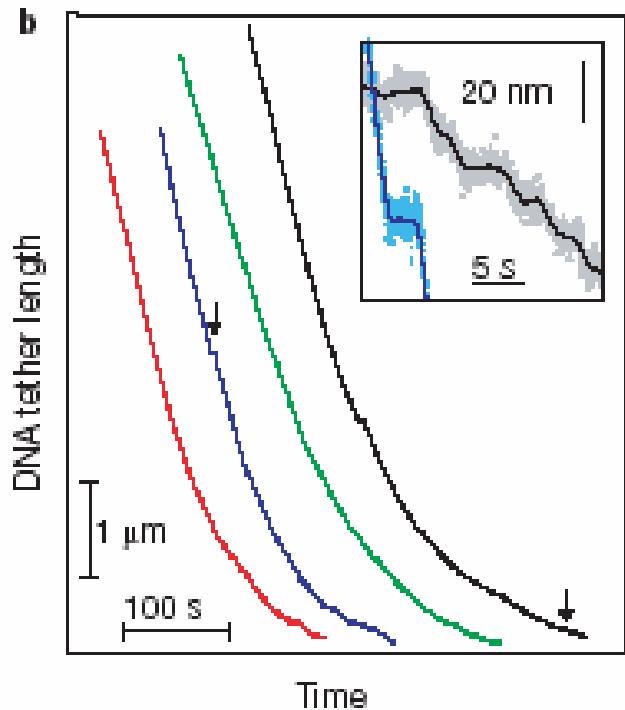
- **Title:** *The bacteriophage ϕ 29 portal motor can package DNA against a large internal force*
- Authors: D.S. Smith, S.J. Tans, S.B. Smith, S. Grimes, D.L. Anderson and C. Bustamante
- **Nature**, vol. 413, 18-Oct-02, pp. 748-752

Experiment Setup



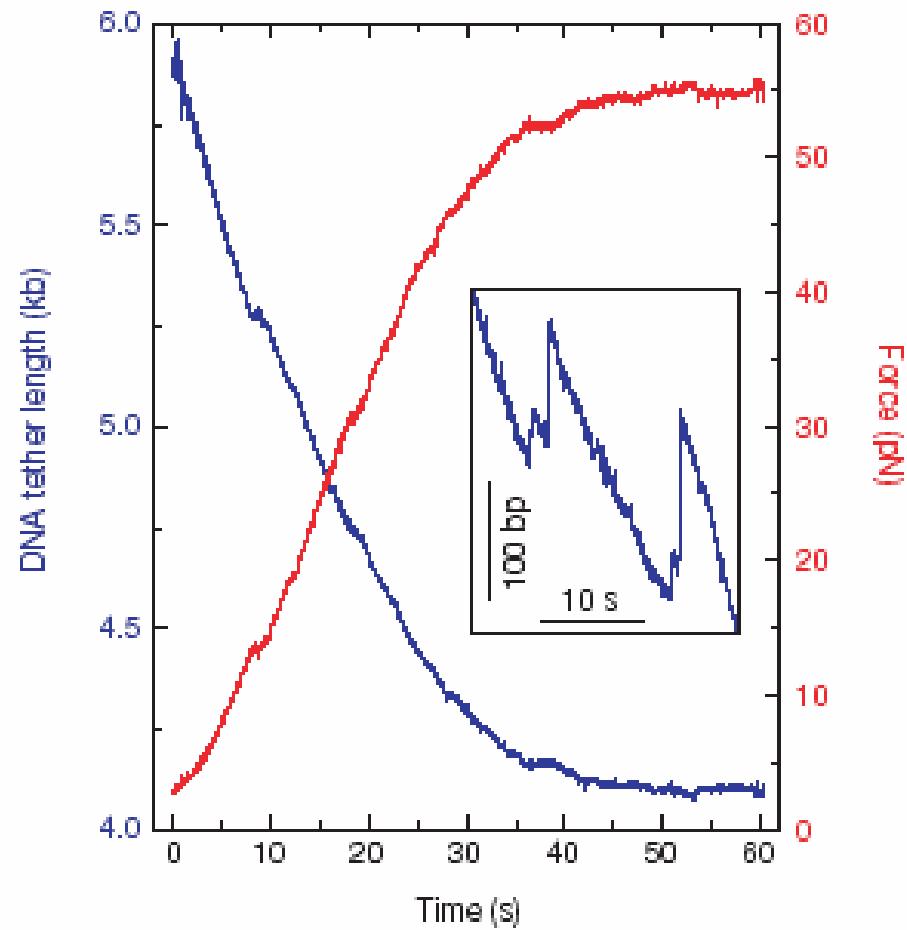
- Capsid: 42x54 nm
- Phage can package its 6.6 μm
- DNA sample: longer than 1.8 times original phage $\phi 29$

Constant Force Feed Back Mode



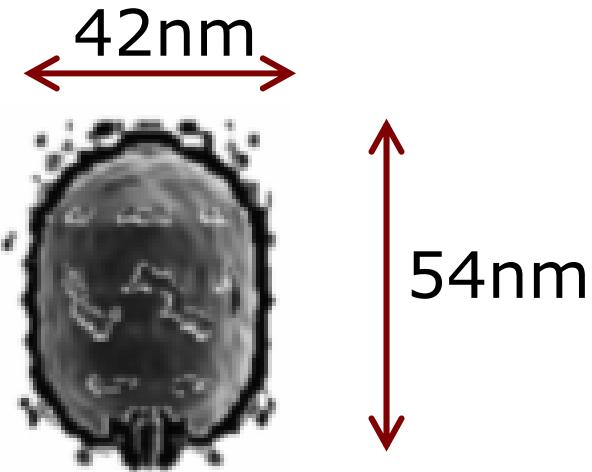
- $F \sim 5 \text{ pN}$
- Using 34.4 kb $\phi 29$ - λ DNA

No Feed-Back Mode

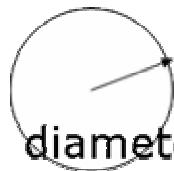


- The force is measured from the laser tweezers
- The stall force is **57 pN** in avg. and distance moved per ATP is **0.68 nm**. Assuming ATP in buffer is **120 pN-nm**, the efficiency of the motor is **30%**
- The pressure in the capsid is known as **6 MPa**, and the thickness of the capsid is **1.6 nm**
- The tensile stress of the capsid wall is **~100 MPa**

Estimate the Bacteriophage ϕ 29 Capsid while the DNA is fully packaged



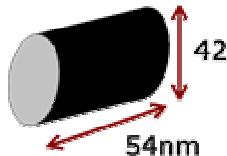
Assume the capsid is sphere:



$$\text{diameter} = (54 + 42) / 2$$
$$\sigma = \frac{pr}{2t} = \frac{6 * \left(\left(\frac{54+42}{2} \right) / 2 \right)}{2 * 1.6} \approx 45 MPa$$

Assume the capsid is vessels:

$$\sigma = \frac{pr}{t} = \frac{6 * \left(\frac{42}{2} \right)}{2 * 1.6} \approx 78.75 MPa$$



Introduction to DNA Chip

Chang Ann Yuan

H.S. Ku

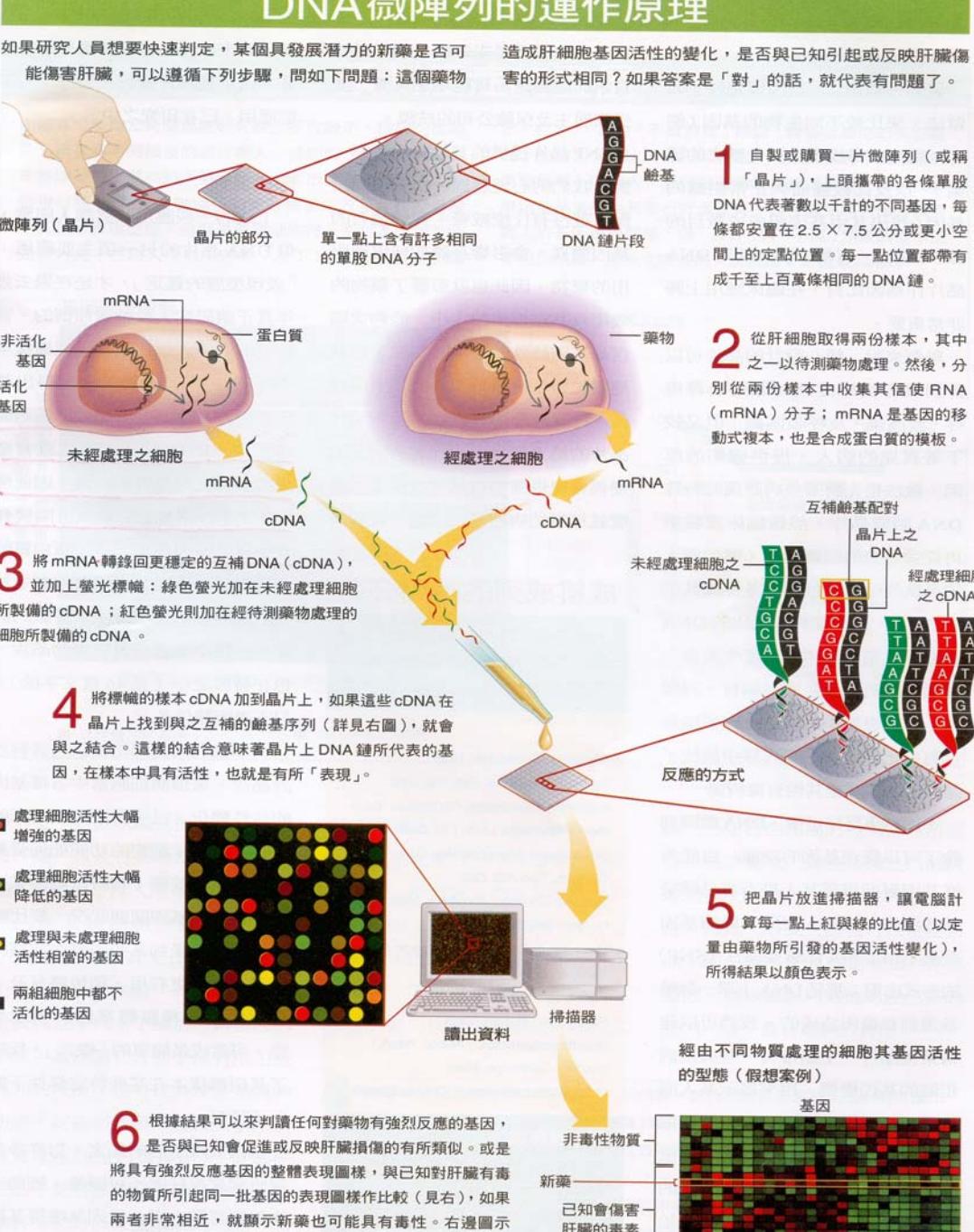
Advisor: Dr. K.N.Chiang

03-Sep-02'

Outline

- DNA Chip Principle
- DNA Chip Type
- DNA Chip Product: Nanogen
- DNA Chip & EP/MEMS Packaging
- New Idea: Reusable DNA Chip

DNA Chip Principle

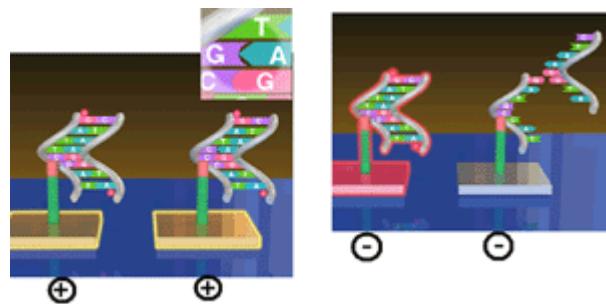
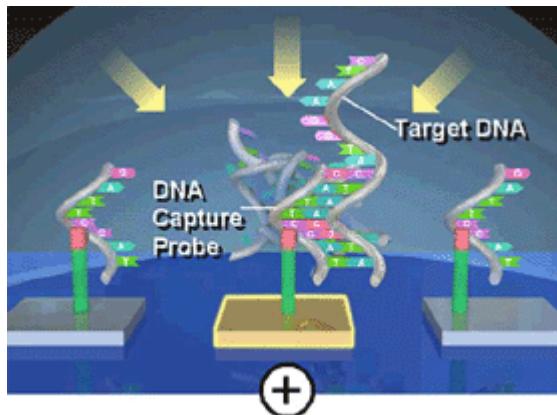


DNA Chip Type

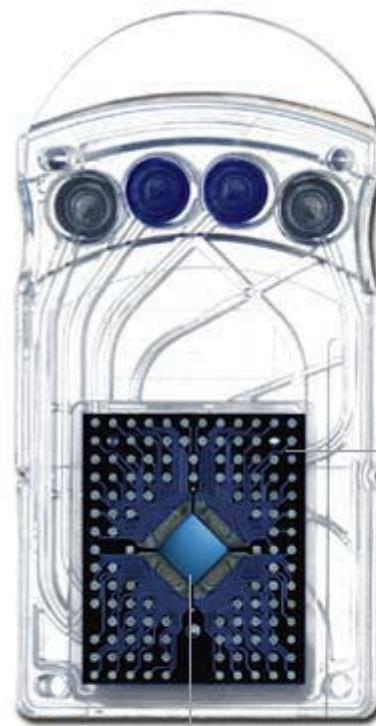
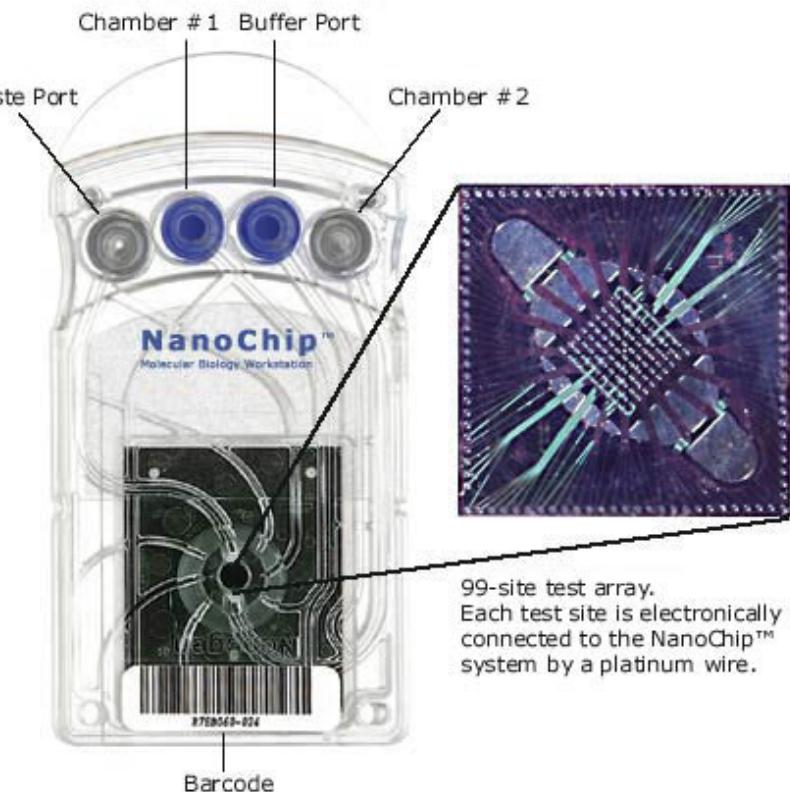
- Probe
 - ✓ Oligonucleotides or Peptide nucleic acids (PNA)
 - ✓ DNA Segments
- Manufacture
 - ✓ Photolithography
 - ✓ Mechanical microspotting
 - ✓ Ink jet

Note: the hybrid time: 10-15 hrs

DNA Chip Product: Nanogen



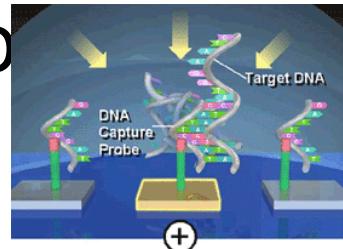
DNA Chip & EP/MEMS Packaging



The microchip is similar to that used in many computers and enables extremely precise control of each individual test site.

The NanoChip™ electronic chip contains platinum wires which are connected to a computer controller once the NanoChip™ is inserted into the NanoChip™ Molecular Biology Workstation.

New Idea of Reusable DNA Chip



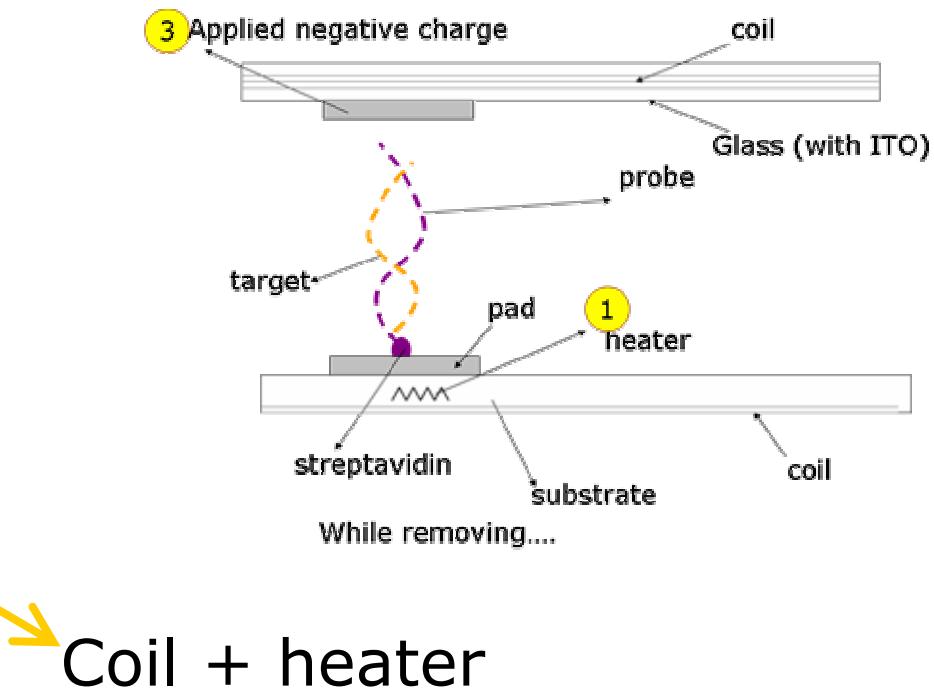
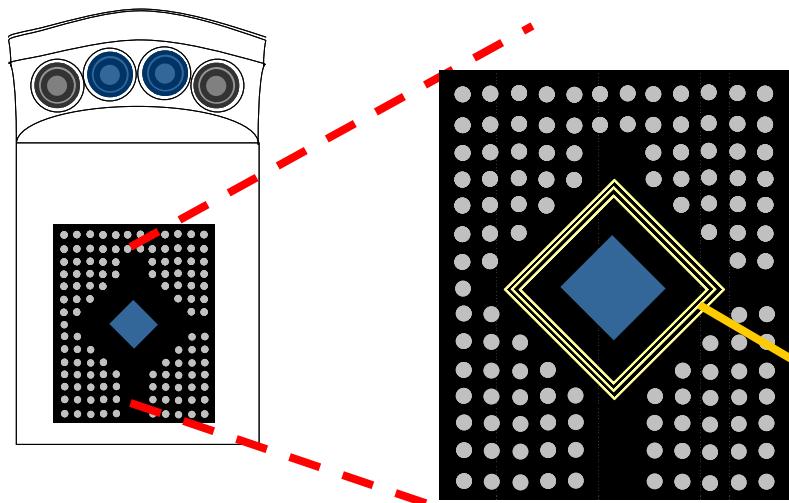
Physical phenomenon

-to remove target DNA segment after testing

✓ RFMF

✓ TM(rising the temperature)

✓ Negative charge



Coil + heater